

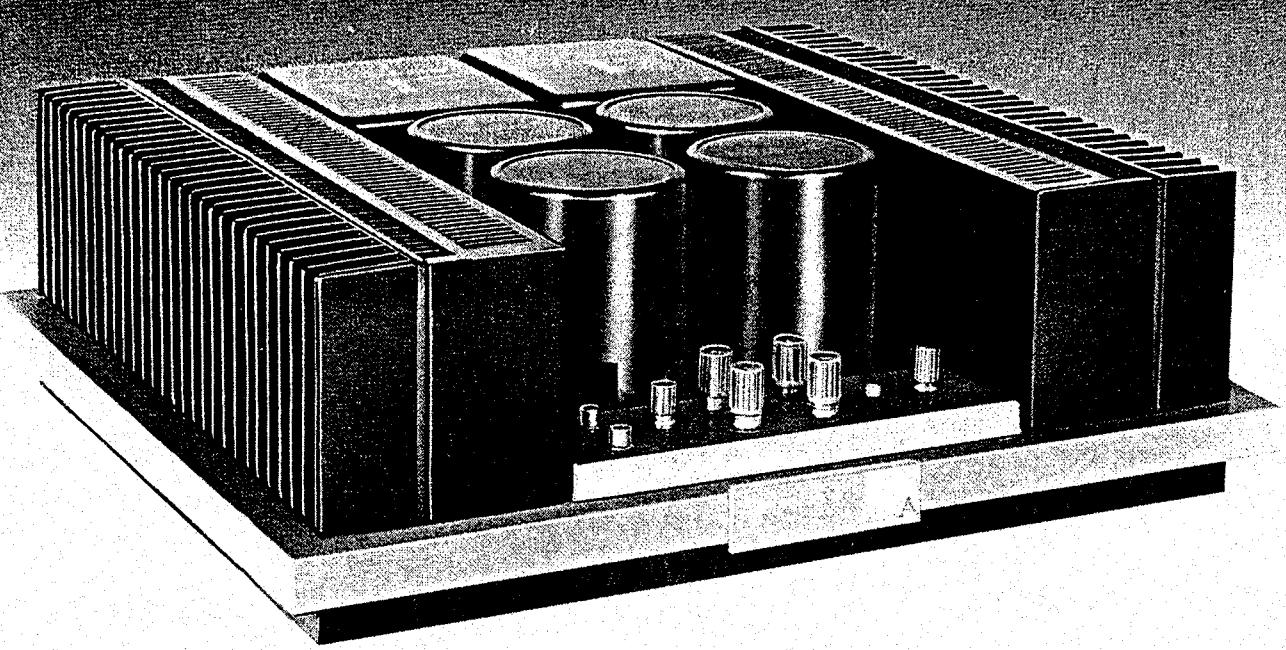


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STEREO POWER AMPLIFIER

M-22

SERVICE MANUAL

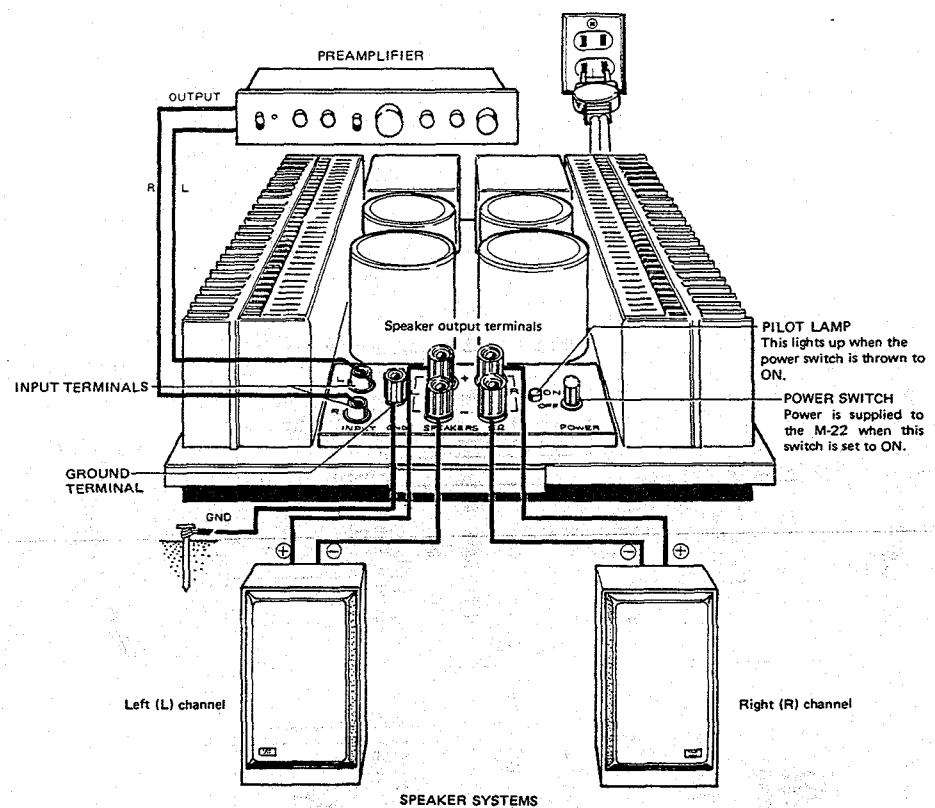


 PIONEER®

1. SPECIFICATIONS

Semiconductors	
Transistors 44
Diodes 66(KL-type), 65(N-type)
Amplifier Section	
Circuitry	2-stage Differential push-pull, 2-stage Darlington connection, parallel push-pull, direct-coupled OCL (Class-A operation)
Continuous Power Output from 10 Hertz to 30,000 Hertz (Both channels driven) 30 watts per channel (8 ohms)
Total Harmonic Distortion at 10Hz to 30,000Hz	
Continuous rated power output 0.01%
15 watts per channel power output, 8 ohms 0.005%
1 watt per channel power output, 8 ohms 0.005%
Intermodulation Distortion (50Hz: 7kHz = 4:1)	
Continuous rated power output 0.01%
15 watts per channel power output, 8 ohms 0.01%
1 watt per channel power output, 8 ohms 0.01%
Frequency Response 2Hertz to 150,000Hertz ±1dB
Input (Sensitivity/Impedance)	
INPUT 1V/50kilohms
Output	
SPEAKER 8 ohms
Damping Factor (20Hertz to 20,000Hertz, 8 ohms) 60
Hum and Noise (IHF, short-circuited, A network) 106dB
Miscellaneous	
Power Requirements 120V 60Hz (KL-type) 220V 50/60Hz (N-type)
Power Consumption 280 watts (UL)
Dimensions 420(W)x153(H)x370(D) mm 16-9/16 - 6-1/32 - 14-9/16 in.
Weight	Without Package: 22kg (48 lb 7 oz) With Package: 24.7 kg (54 lb 6 oz)
Furnished Parts	
Connection Cord with Pin plugs 1
Operating Instructions 1

2. CONNECTION DIAGRAM



NOTE:
Specifications and the design subject to possible modification without notice due to improvements.

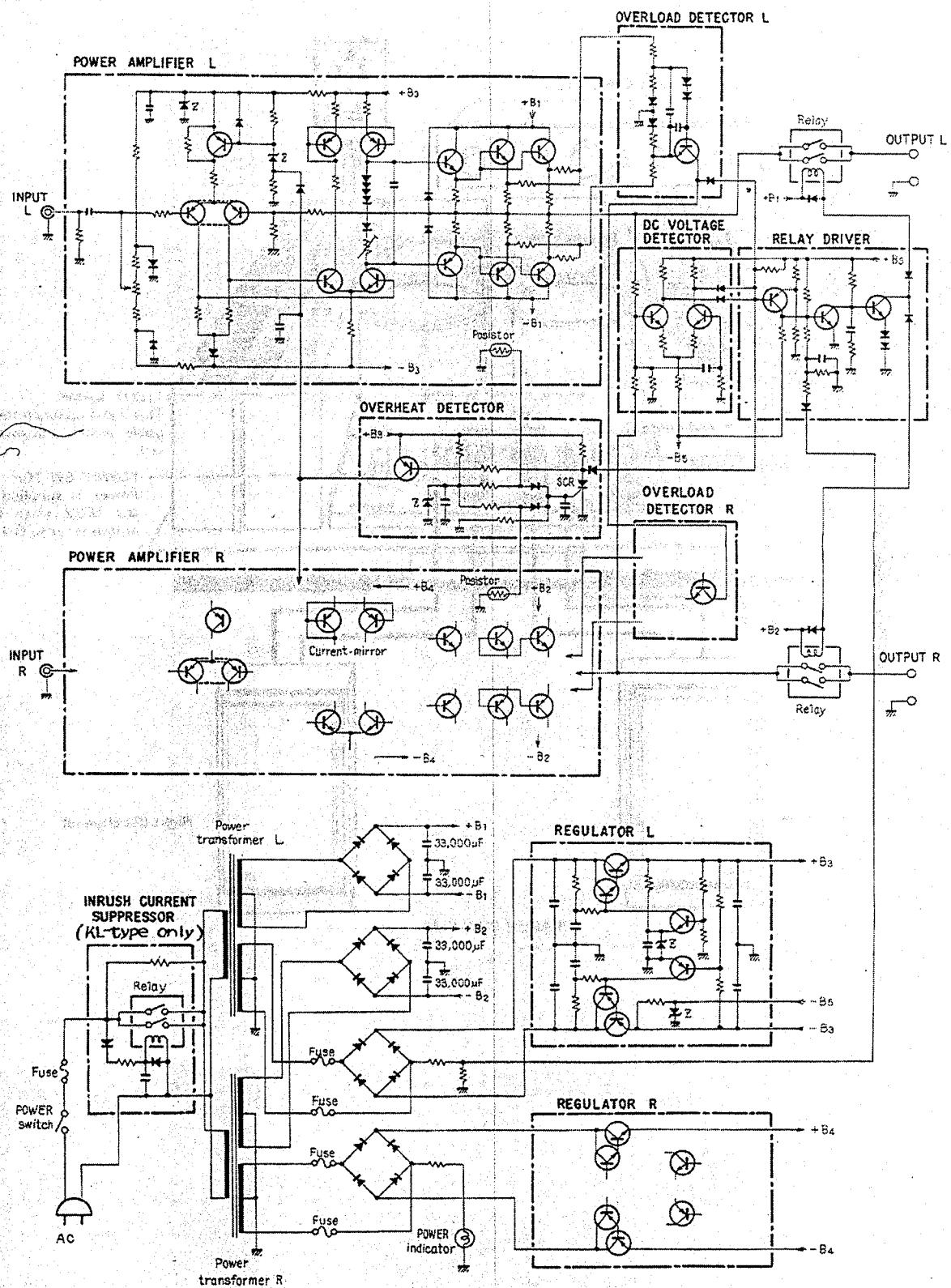
MODEL M-22 COMES IN TWO VERSIONS DISTINGUISHED AS FOLLOWS:

Type	Voltage	Remarks
KL	120V only	U. S. A. model
N	220V only	General export model

CONTENTS

1. SPECIFICATIONS	2
2. CONNECTION DIAGRAM	3
3. BLOCK DIAGRAM	4
4. CIRCUIT DESCRIPTIONS	
4.1 Amplifier Section	5
4.2 Protection Circuit	6
4.3 Power Supply Circuit	8
5. DISASSEMBLY	9
6. PARTS LOCATION	
6.1 Top View	11
6.2 Bottom View	12
7. ADJUSTMENT	13
8. EXPLODED VIEW	14
9. SCHEMATIC DIAGRAMS, P.C. BOARD PATTERNS AND PARTS LIST	
9.1 Miscellanea	21
9.2 Schematic Diagram for KL-type	23
9.3 Schematic Diagram for N-type	25
9.4 AF Power Assembly (AWK-057)	27
9.5 AF Power Assembly (AWK-058)	33
10. PACKING	38

3. BLOCK DIAGRAM



4. CIRCUIT DESCRIPTIONS

4.1 AMPLIFIER SECTION

The first stage is a low noise twin transistor (Q1) differential amplifier. The twin transistor consists of two transistors having the same characteristics mounted in a single unit. Consequently, the two transistors are subjected to the same thermal conditions and are ideal as a differential amplifier. Neutral potential drift is also suppressed by using the forward voltage of silicon diodes D1 and D2 which have matched temperature coefficients in the offset voltage adjustment circuit so that temperature changes are mutually cancelled. The predriver stage is a differential amplifier (Q2, Q3) with current mirror (Q4, Q5) and is operated as a push-pull amplifier. The base of Q4 is connected to the collector and is equivalent to a diode.

The base-to-emitter voltage generated at Q4 by the collector current of Q2 forward biases Q5. Q4 and Q5 are the same type, and if R14 and R15 are equivalent, the emitter current of Q4 and Q5 also becomes equivalent. If the common emitter current transfer ratio of Q4 and Q5 is made sufficiently large, the collector current of Q5 equals the collector current of Q2. Therefore, Q3 and Q5 are operated in a push-pull arrangement.

The power stage is a 2-stage Darlington connection SEPP.

The final stage power transistors are connected in

The idle current is 0.85A/transistor. Operation is Class A.

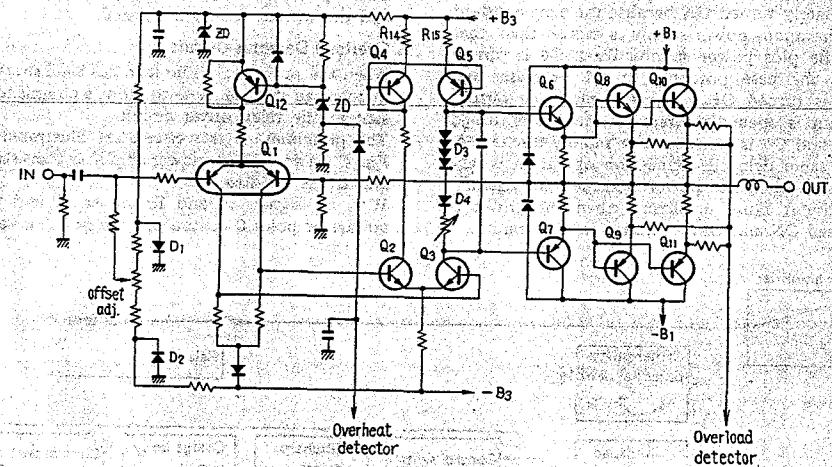


Fig. 1. Basic circuitry of power amplifier.

4.2 PROTECTION CIRCUIT

The amplifier and speakers are safeguarded by a protection circuit which employs a relay to automatically open and close the output circuit. This circuit consists of four parts (Fig. 2).

1. Relay Driver Circuit (Fig. 3)

This circuit controls the operation of the relay. Delay connection at power ON and muting at power OFF and disconnection (see items 2 ~ 4) based on commands from the detection circuits are performed by this circuit.

Muting Operation

When the power is turned ON, the base of Q6 is reverse biased and Q6 remains OFF. Q5 also normally remains OFF. When C4 is charged thru R22 and R23, the base potential of Q7 rises and Q7 is turned ON. Current then flows in the relay coils (RL2, RL3), the relay contacts are closed and the output circuit is connected. When the power is turned OFF, the base of Q6 is momentarily forward biased and Q6 is immediately turned ON because the time constant of the minus power supply is shorter than that of the plus power supply. When Q6 is turned ON, the base potential of Q7 decreases and Q7 is turned OFF. Consequently, the output circuit is opened. Moreover, since Q6 is turned ON and C4 is subsequently rapidly discharged, the same delayed connection operation is performed when the power is turned ON again. Transient noise occurring when the power is turned ON and OFF is muted in this manner.

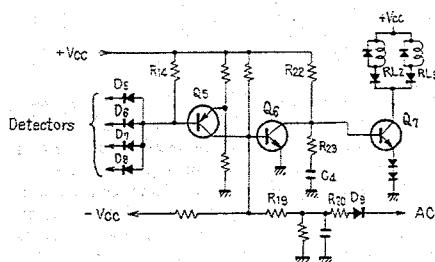


Fig. 3 Relay driver circuit

Operation by Detector Circuit Command

Detector circuit commands are actually current flowing in D5, D6, D7 or D8. Normally, Q5 is in the OFF state. When current flows in D5, D6, D7 or D8, a voltage is generated across R14. This voltage forward biases Q5 turning it ON. Thereupon, Q6 is turned ON, Q7 is turned OFF and the output circuit is opened.

2. Overload Detector Circuit

When the power amplifier load has been shorted or the load impedance is too low, a command is sent to the relay driver circuit.

The principles of this circuit are illustrated in Fig. 4. Qa and Qb are power amplifier transistors and RL is the load.

With no signal, Ia and Ib are equal and the voltage at point C (output neutral point) is zero.

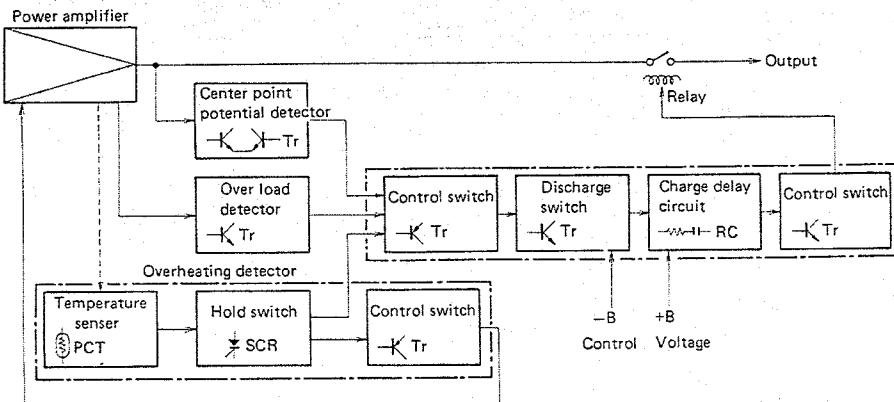


Fig. 2 Block diagram of protection circuit

The voltage at point D is the voltage at point A divided by R1 and R3. The voltage at point E is the voltage at point B divided by R2 and R4. The potential difference between point D and point E is applied between the base and emitter of Q1 thru D3 and D4. However, since this potential difference is lower than the sum of VF (forward voltage) of D3 and D4 and VBE (base-to-emitter voltage) of Q1, base current doesn't flow at Q1 so Q1 is turned OFF.

At the positive half cycle of the signal, Ib increases, Ia decreases, their difference flows through RL and a positive voltage is generated at point C.

Since Qa and Qb are operated in a Class A push-pull configuration, the amount of increase of Ia and the amount of decrease of Ib are equal, and the potential difference between point A and point B remains the same as with no signal. Since D2 is turned OFF by a rise in the voltage at point B, the voltage at point E becomes almost equal to that at point B. Therefore, the difference in potential between point D and point B is applied to the base of Q1 thru D3 and D4. Since the difference between Ia and Ib becomes greater as RL is made smaller, the potential difference between point A and point C becomes larger. Consequently, if RL is too small, the level shift by VF of D3 and D4 is exceeded, current flows in Q1 turning it ON. This causes current to flow in D5. This current becomes a command to the relay driver circuit. If RL is sufficiently large, the voltage of point E becomes higher than that of point D, Q1 is reverse biased and is turned OFF.

At the negative half cycle of the signal, Ib increases, Ia decreases, their resultant current flows through RL and a negative voltage is generated at point C.

Since D1 is turned OFF by the voltage drop at point A, the voltage of point D becomes almost equal to that at point A. Therefore, the difference of potential difference between point A and point E is applied to the base of Q1 thru D3 and D4. Since the difference between Ia and Ib becomes greater as RL is made smaller, the potential difference between point B and point C becomes larger. Consequently, if RL is too small, the level shift by VF of D3 and D4 is exceeded, current flows in Q1 turning it ON. This causes current to flow in D5. This current becomes a command to the relay driver circuit. If RL is sufficiently large, the voltage at point D becomes lower than that at point E, Q1 is reverse biased and is turned OFF.

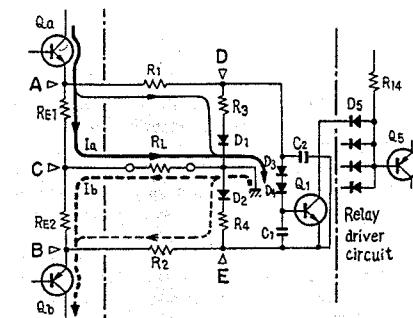


Fig. 4 Overload detector circuit

3. Center Point Potential Detector Circuit

When a DC potential is generated at the output center point of the power amplifier, a command is sent to the relay driver circuit. The principles of this circuit are illustrated in Fig. 5. Q3 and Q4 form a differential amplifier. Therefore, there is no output even if the same input is applied to the base of both transistors. The output center point is normally only an AC signal. Since the reactance of C2 is sufficiently low, the same signal is applied to Q3 and Q4 and no output appears at their collectors.

When a DC potential is produced at the output center point, input is only applied to Q3. If this DC potential is positive, the collector current of Q3 increases and the collector current of Q4 decreases. Therefore, the collector voltage of Q3 drops and current flows in D7. If the DC voltage produced at the output center point is negative, the collector current of Q4 increases. Therefore, the collector voltage of Q4 drops and current flows in D6.

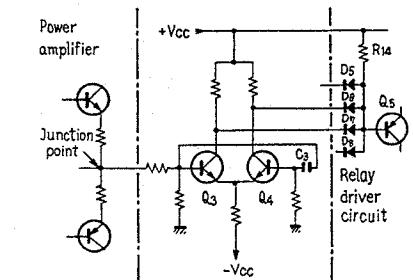


Fig. 5 Center point potential detector

4. Overheating Detector Circuit

This circuit detects overheating of the heat sink for the power transistors.

A PCT (Positive Coefficient Thermistor) is used as the sensor. When the temperature of the PCT exceeds the rated temperature, its resistance increases abruptly.

Q9 and Q10 in Fig. 6 are the first stage of the power amplifier. Q8 is normally in the OFF state and Q9 provides constant-current drive for the differential amplifier (Q10).

The PCT is mounted at the heat sink and its resistance increases abruptly when the temperature of the heat sink exceeds the specified value. Thereupon, the gate voltage of the SCR (Silicon Controlled Rectifier) exceeds the trigger voltage and the SCR is turned ON. This causes current to flow in D8. This current is sent to the relay driver circuit as a command. Moreover, at this time Q8 is also turned ON and the base voltage of Q9 increases and Q9 is turned OFF. This causes the power amplifier to be placed in the cutoff state, almost no current flows in the power transistors and the excessive calorific value is reduced.

Once turned ON, the SCR remains ON as long as the current does not fall below the holding current. Therefore, once this detector circuit has been operated, the output circuit remains open and the power amplifier remains in the cutoff state even if the temperature of the heat sink falls below the specified temperature. The power must be turned OFF to reset the detector circuit.

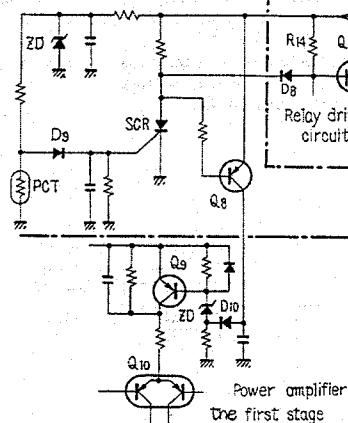


Fig. 6 Overheating detector circuit

4.3 POWER SUPPLY CIRCUIT

Two power transformers are used and the power amplifier power supplies are independent for the left and right channels.

Positive and negative voltages are supplied to the power stage by a bridge rectifier and $33000\mu F$ ($\times 2$) capacitors. Positive and negative voltages are supplied to the drive stage from separate windings (other than those used for the power stage) by a bridge rectifier and plus and minus voltage regulators.

Inrush Current Suppressor Circuit

NOTE:

This circuit is only applicable to model (KL-type) having 120V primary voltage.

An extremely large inrush current flows in equipment having two high capacity power supplies, such as this unit, when the power is turned ON. This circuit suppresses this inrush current.

Resistor R1 is inserted in series with the primary windings of the power transformers. Since the inrush current flows thru R1 when the power is turned ON, it is suppressed substantially. When C1 is charged thru D1 and R2, the contacts of the relay are closed and R1 is shorted. The time required for this is made sufficiently shorter than the muting time of the output circuit at power ON so that normal operation is not effected.

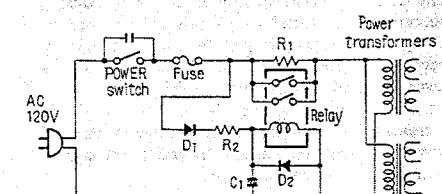
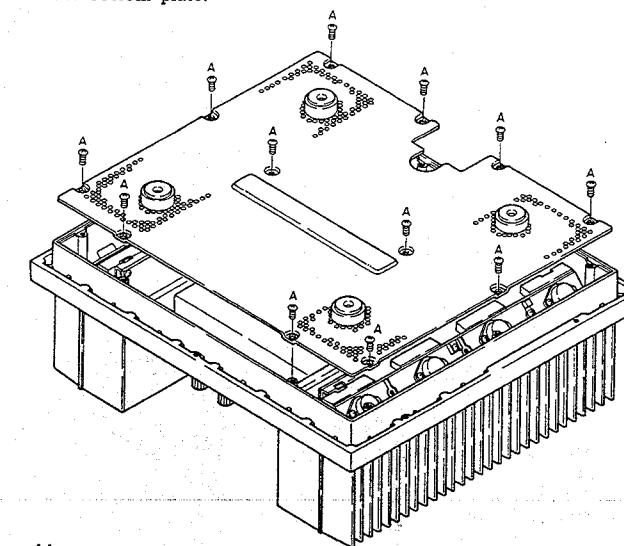


Fig. 7 Inrush current suppressor circuit

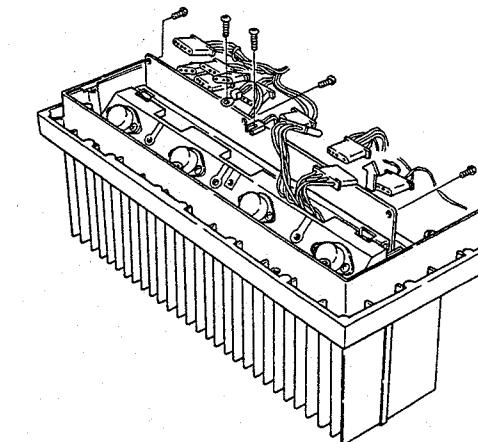
5. DISASSEMBLY

Remove the 12 mounting screws(A) at the bottom plate and lift off the bottom plate.



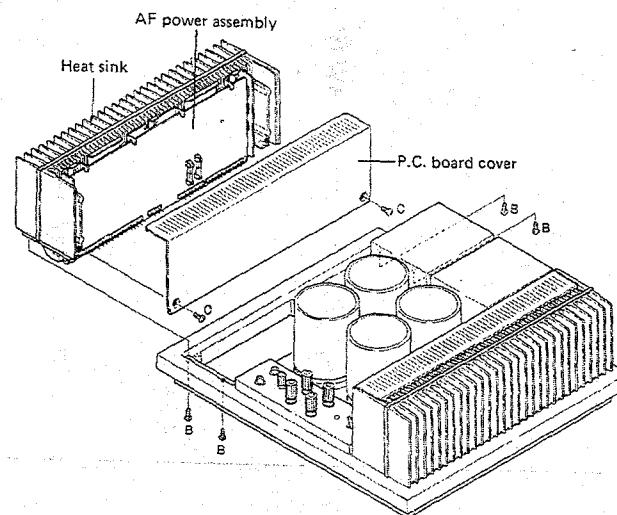
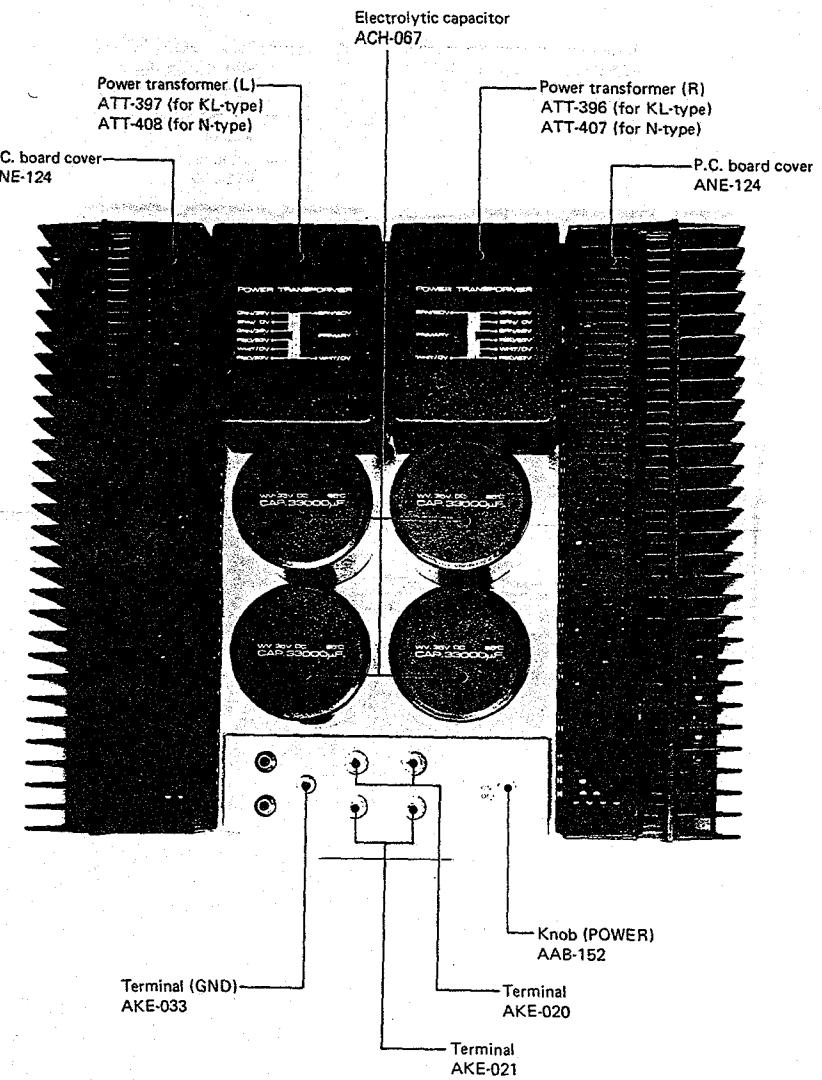
AF Power Assembly

Disconnect the connectors and remove the 5 screws.
Pull off the P.C. board.

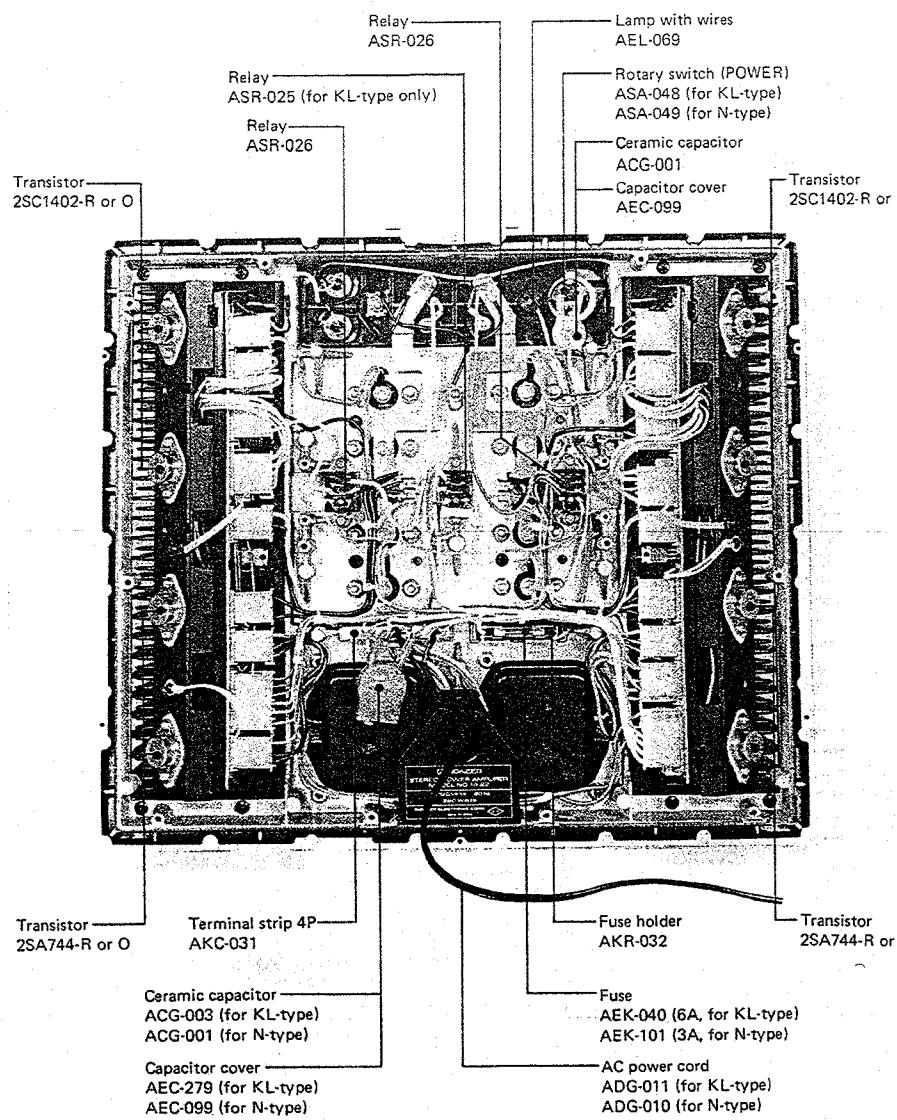


Heat Sink

Remove the 4 screws(B)

**6. PARTS LOCATION****6.1 TOP VIEW**

6.2 BOTTOM VIEW



7. ADJUSTMENT

- Open both the input and output terminals.
- Perform the measurement with a DC voltmeter.
- AWK-057 is the left channel printed circuit board and AWK-058 is the right channel printed circuit board.

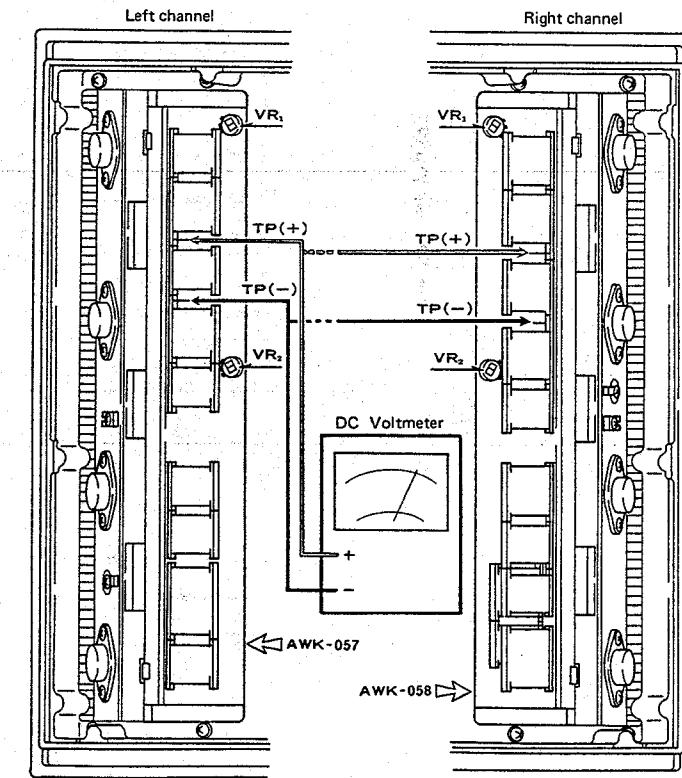
DC Balance Adjustment

Adjust VR1 for +80mV between the (+) and (-) output terminals.

Idle Current Adjustment

Adjust VR2 for 850mV between the TP terminals.
Readjust after 10 minutes.

NOTE:
Idle current is 1.7A (0.85A/transistor).



8. EXPLODED VIEW

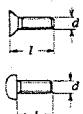
The following symbols stand for screws, washers and nuts as shown in exploded view.

Symbol	Description	Shape
RT	Brazier head tapping screw	
PT	Pan head tapping screw	
BT	Binding head tapping screw	
CT	Countersunk head tapping screw	
TT	Truss head tapping screw	
OCT	Oval countersunk head tapping screw	
PM	Pan head machine screw	
CM	Countersunk head machine screw	
OCM	Oval countersunk head machine screw	
TM	Truss head machine screw	
BM	Binding head machine screw	
PSA	Pan head screw with spring lock washer	
PSB	Pan head screw with spring lock washer and flat washer	
PSF	Pan head screw with flat washer	

Symbol	Description	Shape
EW	E type washer	
FW	Flat washer	
SW	Spring lock washer	
N	Nut	
WN	Washer faced nut	
ITW	Internal toothed lock washer	
OTW	External toothed lock washer	
SC	Slotted set screw (Cone point)	
SF	Slotted set screw (Flat point)	
HS	Hexagon socket headless set screw	
OCW	Oval countersunk head wood screw	
CW	Countersunk head wood screw	
RW	Round head wood screw	

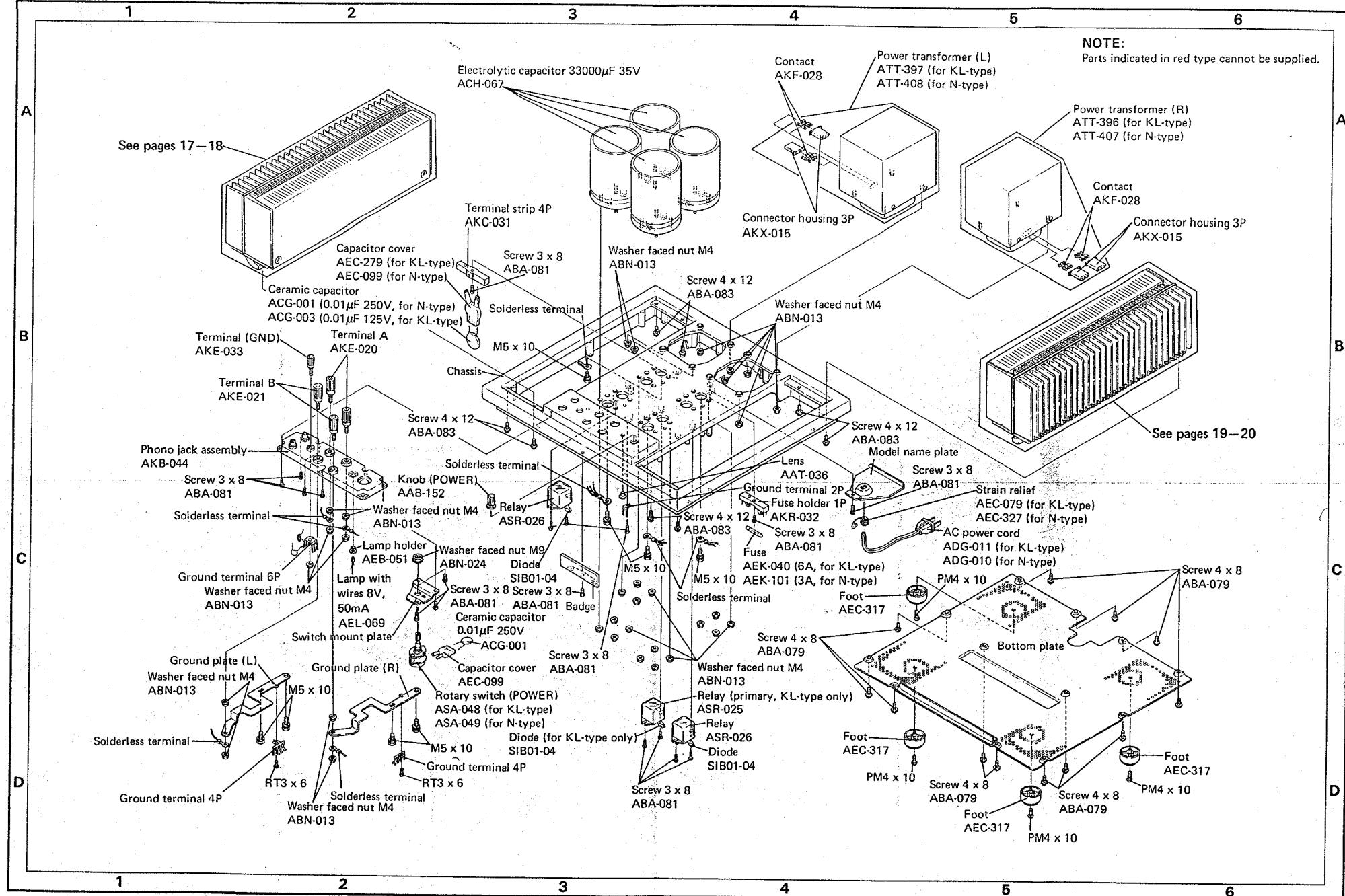
EXAMPLE

PM	3	x	8
length in mm (l)			
diameter in mm (d)			
Symbol			



FW	90	x	1
thickness in mm (t)			
diameter in mm (d)			
Symbol			





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Power Amplifier Block (L)

NOTE:
Parts indicated in red type cannot be supplied.

A

A

B

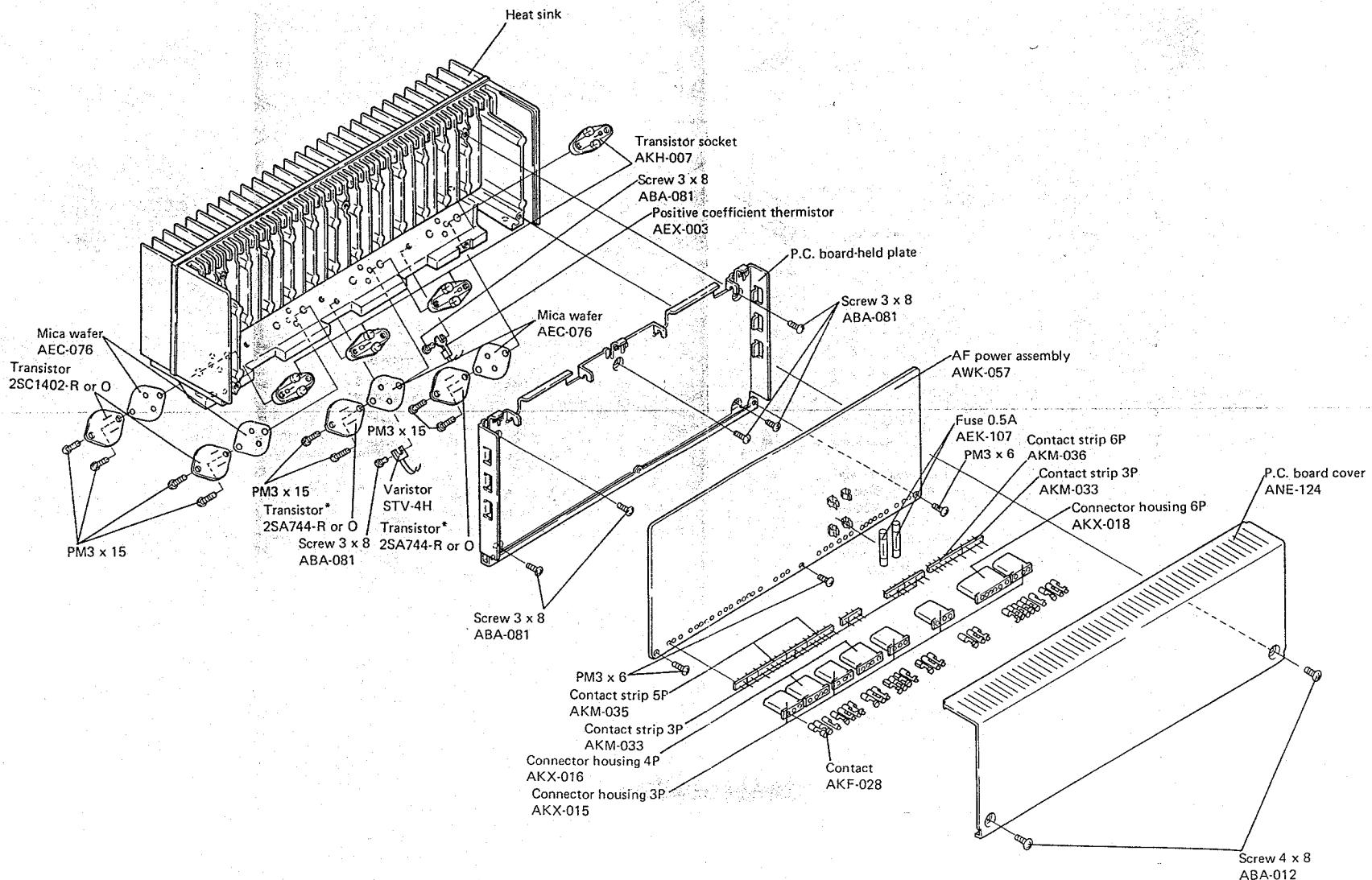
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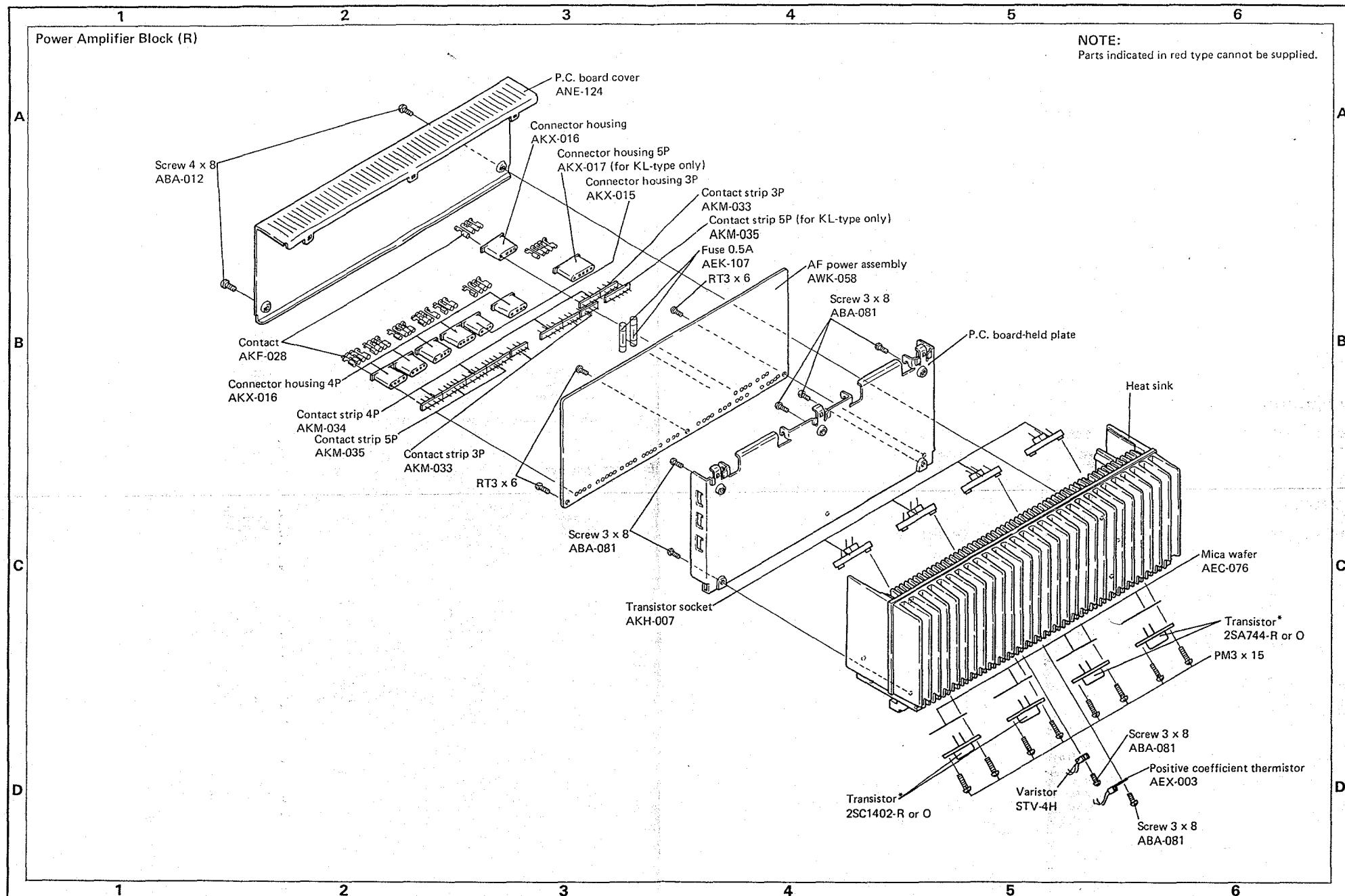
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D

D





9. SCHEMATIC DIAGRAMS, P. C. BOARD PATTERNS AND PARTS LIST

9.1 MISCELLANEA

Miscellaneous Parts

NOTE:

- Capacitors: in μF unless otherwise noted p:pF
- Resistors: in Ω , $\frac{1}{4}\text{W}$ unless otherwise noted k:k Ω , M:M Ω

FUSE

<u>Symbol</u>	<u>Description</u>	<u>Part No. (KL-type)</u>	<u>Part No. (N-type)</u>	<u>Remarks</u>
FU1	Fuse 6A	AEK-040	
	Fuse 3A	AEK-101	
FU2	Fuse 0.5A	AEK-107	AEK-107	
FU3	Fuse 0.5A	AEK-107	AEK-107	
FU4	Fuse 0.5A	AEK-107	AEK-107	
FU5	Fuse 0.5A	AEK-107	AEK-107	

TRANSFORMERS

<u>Symbol</u>	<u>Description</u>	<u>Part No. (KL-type)</u>	<u>Part No. (N-type)</u>	<u>Remarks</u>
T1	Power transformer	ATT-396	ATT-407	Rch.
T2	Power transformer	ATT-397	ATT-408	Lch.

CAPACITORS

<u>Symbol</u>	<u>Description</u>	<u>Part No. (KL-type)</u>	<u>Part No. (N-type)</u>	<u>Remarks</u>
C1	Ceramic 0.01 250V	ACG-001	ACG-001	
C2	Ceramic 0.01 250V	ACG-001	ACG-001	
C3	Ceramic 0.01 250V	ACG-001	ACG-001	
C4	Ceramic 0.01 250V	ACG-001	ACG-001	
C5	Ceramic 0.01 250V	ACG-001	ACG-001	
C6	Ceramic 0.01 125V	ACG-003	
	Ceramic 0.01 250V	ACG-001	

SEMICONDUCTORS

<u>Symbol</u>	<u>Description</u>	<u>Part No.</u>	<u>Remarks</u>
Q1	Transistor	2SC1402-R or O	
Q2	Transistor	2SA744-R or O	
Q3	Transistor	2SC1402-R or O	
Q4	Transistor	2SA744-R or O	
Q5	Transistor	2SC1402-R or O	
Q6	Transistor	2SA744-R or O	
Q7	Transistor	2SC1402-R or O	
Q8	Transistor	2SA744-R or O	

* hfe of these transistors (Q1—Q8) should have the same value (matched pair).

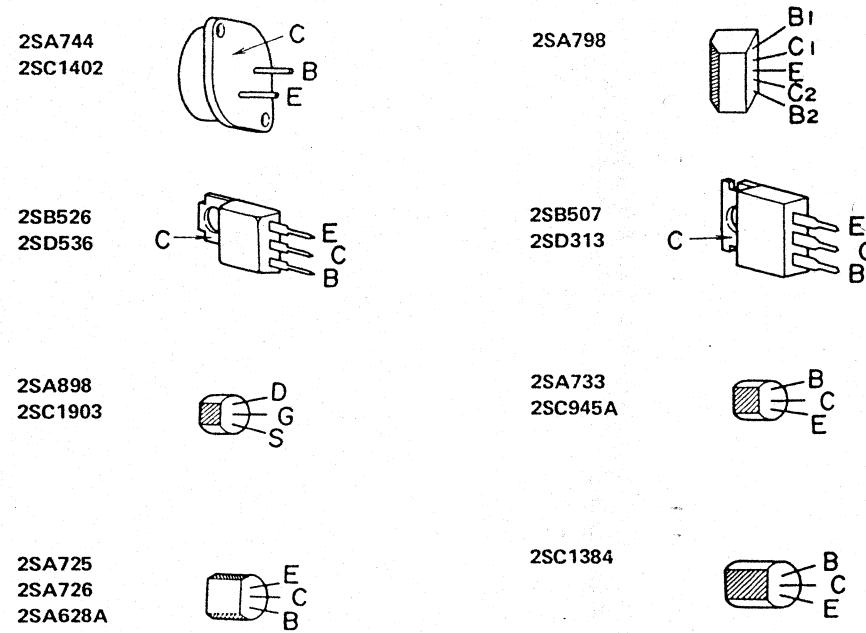
D1	Diode	SIB01-04
D2	Diode	SIB01-04
D3	Diode	SIB01-04

KL-type only

OTHERS

<u>Symbol</u>	<u>Description</u>	<u>Part No. (KL-type)</u>	<u>Part No. (N-type)</u>	<u>Remarks</u>
PL1	Lamp with wires 8V, 50mA	AEL-069	AEL-069	
S1	Rotary switch (POWER)	ASA-048	ASA-049	
RL1	Relay (primary)	ASR-025	
RL2	Relay	ASR-026	ASR-026	
RL3	Relay	ASR-026	ASR-026	
	Terminal strip 4P	AKC-031	AKC-031	
	Fuse holder 1P	AKR-032	AKR-032	
	AC power cord	ADG-011	ADG-010	
R1	Carbon film resistor 2.2k $\frac{1}{4}\text{W}$	RD1%PS 222J	

External Appearances of Transistors



<u>Symbol</u>	<u>Description</u>	<u>Part No.</u>	<u>Symbol</u>	<u>Description</u>	<u>Part No.</u>
D7	Diode	1S2473 (1S1555)	D36	Diode	1S2473 (1S1555)
D8	Varistor	STV-4H	D37	Diode	1S2473 (1S1555)
D9	Diode	1S2473 (1S1555)	D38	Diode	1S2473 (1S1555)
D10	Diode	SR3AM-8			
D11	Diode	SR3AM-8			
D12	Diode	10E2 (1S1885)			
D13	Diode	10E2 (1S1885)			
D14	Diode	10E2 (1S1885)			
D15	Diode	10E2 (1S1885)			
D16	Zener diode	WZ-240			
D17	Zener diode	WZ-130			
D18	Diode	1S2473 (1S1555)			
D19	Diode	1S2473 (1S1555)			
D20	Diode	1S2473 (1S1555)			
D21	Diode	1S2473 (1S1555)			
D21	Diode	1S2473 (1S1555)			
D23	Diode	1S2473 (1S1555)			
D24	Diode	1S2473 (1S1555)			
D25	Diode	1S2473 (1S1555)			
D26	Zener diode	WZ-130			
D27	Diode	1S2473 (1S1555)			
D28	Diode	1S2473 (1S1555)			
D29	SCR	CR02AM-2			
D30	Diode	1S2473 (1S1555)			
D31	Diode	1S2473 (1S1555)			
D32	Diode	1S2473 (1S1555)			
D33	Diode	1S2473 (1S1555)			
D34	Diode	1S2473 (1S1555)			
D35	Diode	1S2473 (1S1555)			

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AF Power Assembly (AWK-057)

A

A

B

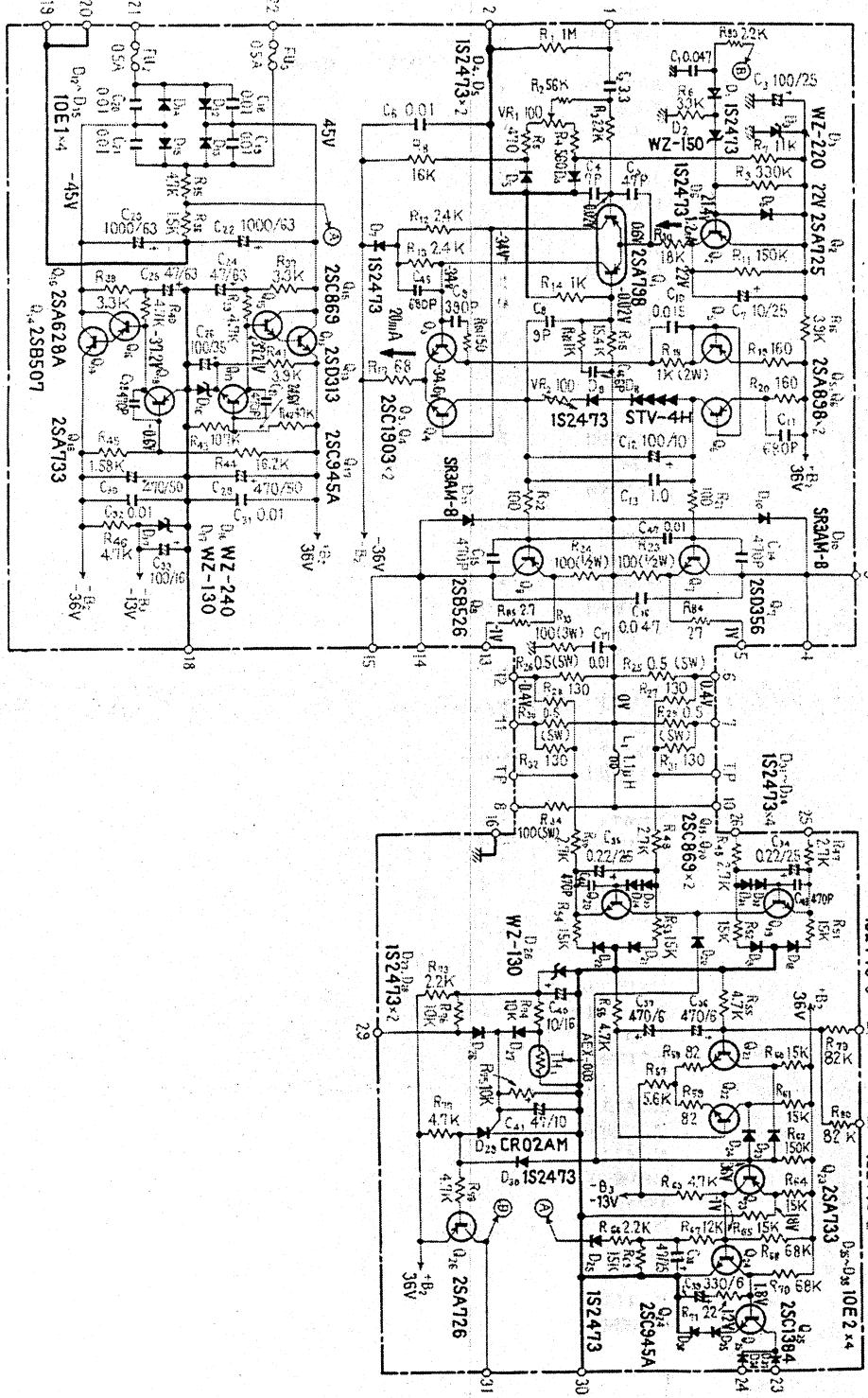
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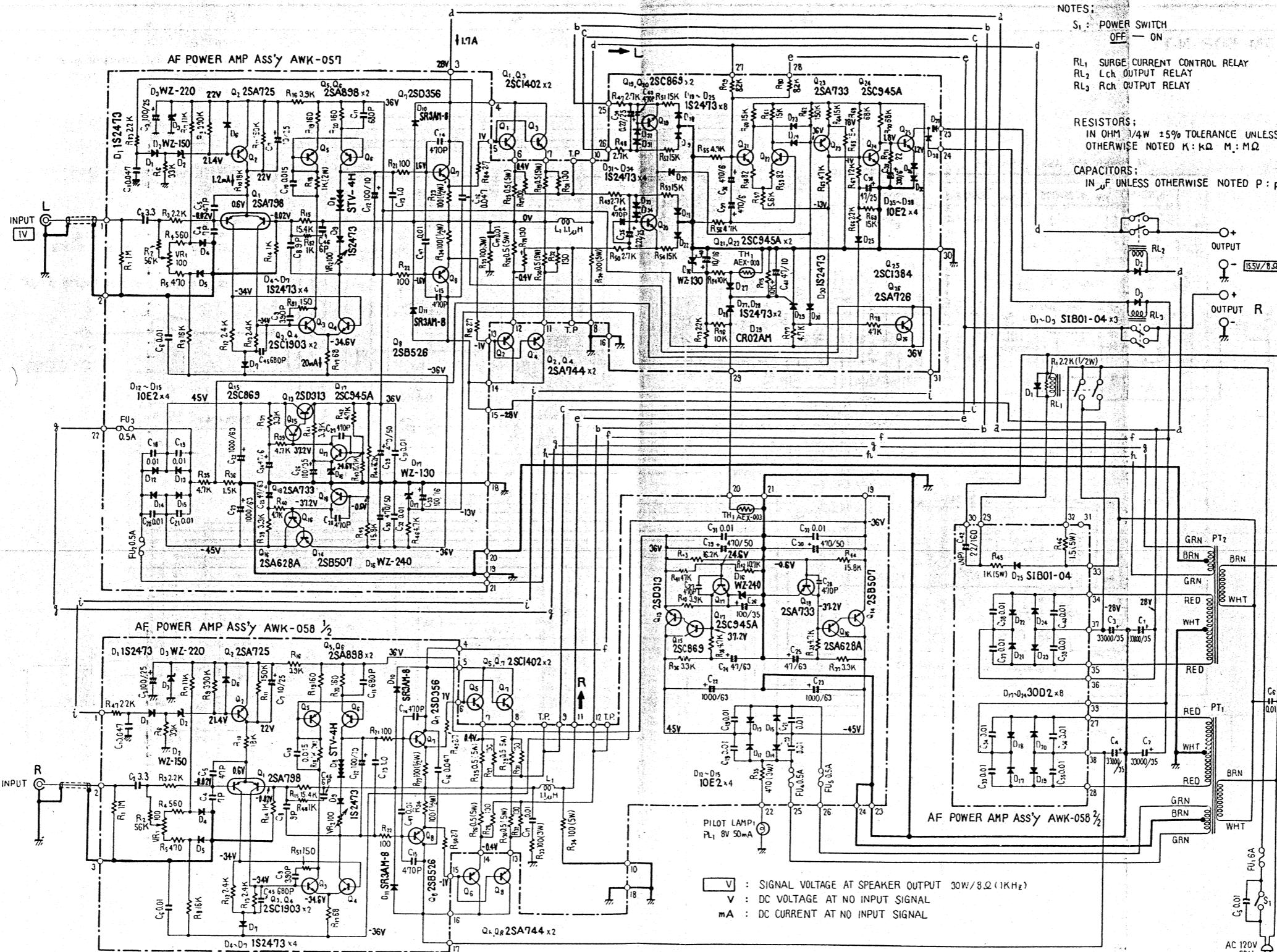
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9.2 SCHEMATIC DIAGRAM FOR KL-TYPE



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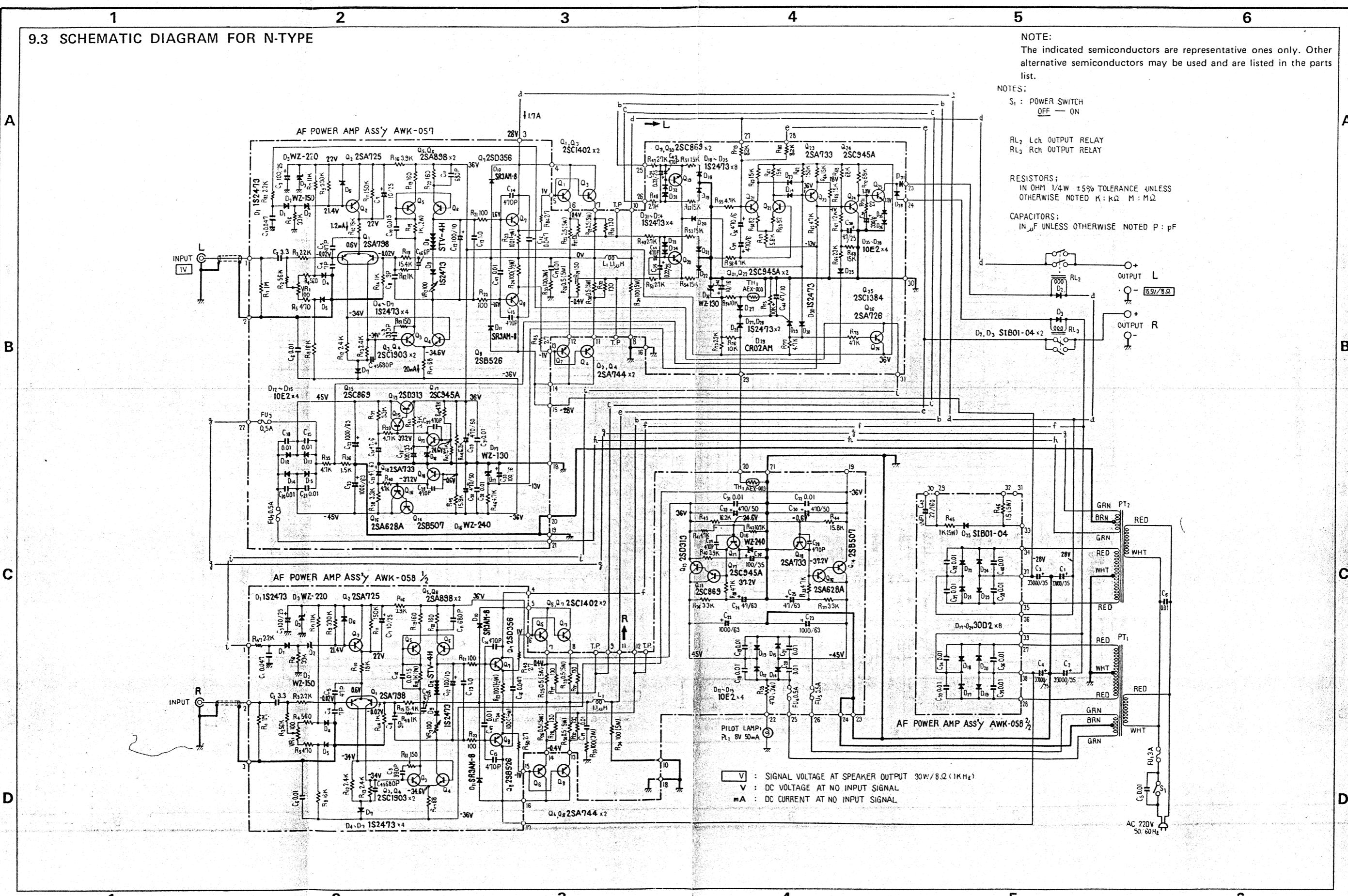
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9.3 SCHEMATIC DIAGRAM FOR N-TYPE



9.4 AF POWER ASSEMBLY (AWK-057)

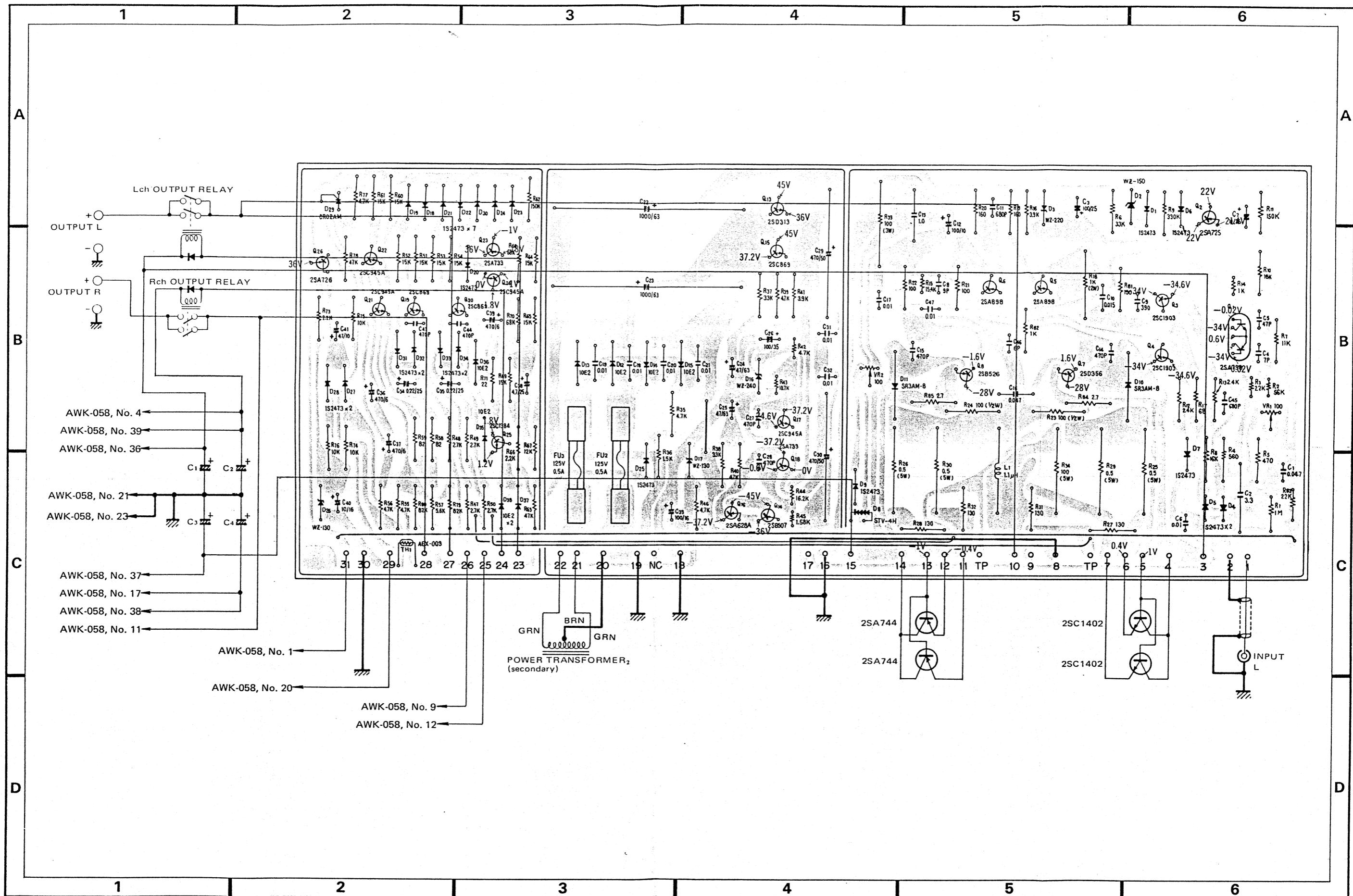
OTHERS

<u>Symbol</u>	<u>Description</u>	<u>Part No.</u>	<u>Symbol</u>	<u>Description</u>	<u>Part No.</u>
L1	AF choke coil 1.1μH Fuse clip	ATH-012 AKR-013	C41	Electrolytic	47 10V
	Contact strip 3P	AKM-033	C42	Vacancy	CEA 470P 16
	Contact strip 5P	AKM-035	C43	Ceramic	470p 50V CKDYB 471K 50
	Contact strip 6P	AKM-036	C44	Ceramic	470p 50V CKDYB 471K 50
	Heat sink (small) Sponge	ANH-317 AEC-387	C45	Ceramic	680p 50V CKDYB 681K 50
			C46	Ceramic	6p 50V CKDYB 060F 50
			C47	Mylar	0.01 50V CQMA 103J 50

CAPACITORS

<u>Symbol</u>	<u>Description</u>	<u>Part No.</u>
C1	Mylar 0.047	50V CQMA 473J 50
C2	Metallized mylar 3.3	100V ACE-013
C3	Electrolytic 100	25V CEA 101P 25
C4	Ceramic 7p	50V CCDSL 070F 50
C5	Ceramic 47p	50V CCDSL 470K 50
C6	Ceramic 0.01	50V CKDYF 103Z 50
C7	Electrolytic 10	25V CEA 100P 25
C8	Ceramic 9p	50V CCDSL 090F 50
C9	Ceramic 390p	50V CCDSL 391J 50
C10	Mylar 0.015	50V CQMA 153J 50
C11	Ceramic 680p	50V CKDYB 681K 50
C12	Electrolytic 100	10V CEA 101P 10
C13	Metallized mylar 1	100V ACE-008
C14	Ceramic 470p	50V CKDYB 471K 50
C15	Ceramic 470p	50V CKDYB 471K 50
C16	Mylar 0.047	100V CQMA 473J 100
C17	Mylar 0.01	50V CQMA 103J 50
C18	Ceramic 0.01	150V ACG-004
C19	Ceramic 0.01	150V ACG-004
C20	Ceramic 0.01	150V ACG-004
C21	Ceramic 0.01	150V ACG-004
C22	Electrolytic 1000	63V ACH-319
C23	Electrolytic 1000	63V ACH-319
C24	Electrolytic 47	63V CEA 470P 63
C25	Electrolytic 47	63V CEA 470P 63
C26	Electrolytic 100	35V CEA 101P 35
C27	Ceramic 470p	50V CKDYB 471K 50
C28	Ceramic 470p	50V CKDYB 471K 50
C29	Electrolytic 470	50V CEB 471P 50
C30	Electrolytic 470	50V CEB 471P 50
C31	Ceramic 0.01	50V CKDYF 103Z 50
C32	Ceramic 0.01	50V CKDYF 103Z 50
C33	Electrolytic 100	16V CEA 101P 16
C34	Electrolytic 0.22	25V CSSA R22M 25
C35	Electrolytic 0.22	25V CSSA R22M 25
C36	Electrolytic 470	6V CEA 471P 6
C37	Electrolytic 470	6V CEA 471P 6
C38	Electrolytic 4.7	25V CEA 4R7P 25
C39	Electrolytic 330	6V CEA 331P 6
C40	Electrolytic 10	16V CEA 100P 16

<u>Symbol</u>	<u>Description</u>	<u>Part No.</u>	<u>Symbol</u>	<u>Description</u>	<u>Part No.</u>	<u>Symbol</u>	<u>Description</u>	<u>Part No.</u>
R31	Carbon film 130	RD1PS 131J	R81	Carbon film 150	RD1PS 151J			
R32	Carbon film 130	RD1PS 131J	R82	Carbon film 1k	RD1PS 102J			
R33	Metal oxide 100	3W RS3P 101J	R83	Carbon film 2.2k	RD1PS 222J			
R34	Wire wound 100	5W RT5B 101K	R84	Carbon film 2.7	RD1PS 2R7J			
R35	Carbon film 4.7k	RD1PS 472J	R85	Carbon film 2.7	RD1PS 2R7J			
R36	Carbon film 1.5k	RD1PS 152J	SEMICONDUCTORS					
R37	Carbon film 33k	RD1PS 333J	<u>Symbol</u>	<u>Description</u>	<u>Part No.</u>			
R38	Carbon film 33k	RD1PS 333J	Q1	Transistor	2SA798-F or G			
R39	Carbon film 47k	RD1PS 473J	Q2	Transistor	2SA725-F or G			
R40	Carbon film 47k	RD1PS 473J	Q3	Transistor	2SC1903-B or V			
R41	Carbon film 3.9k	RD1PS 392J	Q4	Transistor	2SC1903-B or V			
R42	Metal film 4.7k	1/5W RN1/5SQ 4701F	Q5	Transistor	2SA898-B or V			
R43	Metal film 10.7k	1/5W RN1/5SQ 1072F	Q6	Transistor	2SA898-B or V			
R44	Metal film 16.2k	1/5W RN1/5SQ 1622F	Q7*	Transistor	2SD356-D or C			
R45	Metal film 15.8k	1/5W RN1/5SQ 1582F	Q8*	Transistor	2SB526-D or C			
R46	Carbon film 4.7k	RD1PS 472J	* hfe of Q7 and Q8 should have the same value (matched pair).					
R47	Carbon film 2.7k	RD1PS 272J	Q13	Transistor	2SD313-D or E			
R48	Carbon film 2.7k	RD1PS 272J	Q14	Transistor	2SB507-D or E			
R49	Carbon film 2.7k	RD1PS 272J	Q15	Transistor	2SC869-D or C			
R50	Carbon film 2.7k	RD1PS 272J	Q16	Transistor	2SA628A-D or C			
R51	Carbon film 15k	RD1PS 153J	Q17	Transistor	2SC945A-P or Q			
R52	Carbon film 15k	RD1PS 153J	Q18	Transistor	2SA733-R or Q			
R53	Carbon film 15k	RD1PS 153J	Q19	Transistor	(2SA823-P or Q)			
R54	Carbon film 15k	RD1PS 153J	Q20	Transistor	2SC869-D or C			
R55	Carbon film 4.7k	RD1PS 472J	Q21	Transistor	2SC869-D or C			
R56	Carbon film 4.7k	RD1PS 472J	Q22	Transistor	2SC945A-P or Q			
R57	Carbon film 5.6k	RD1PS 562J	R61	Carbon film 15k	(2SC1647-P or Q)			
R58	Carbon film 82	RD1PS 820J	R62	Carbon film 150k	2SC945A-P or Q			
R59	Carbon film 82	RD1PS 820J	R63	Carbon film 4.7k	(2SC1647-P or Q)			
R60	Carbon film 15k	RD1PS 153J	R64	Carbon film 15k	2SA733-R or Q			
R61	Carbon film 15k	RD1PS 153J	R65	Carbon film 15k	(2SA823-P or Q)			
R62	Carbon film 150k	RD1PS 154J	R66	Carbon film 2.2k	2SC945A-P or Q			
R63	Carbon film 4.7k	RD1PS 472J	R67	Carbon film 12k	(2SC1647-P or Q)			
R64	Carbon film 15k	RD1PS 153J	R68	Carbon film 68k	2SC1384-R or S			
R65	Carbon film 15k	RD1PS 153J	R69	Carbon film 15k	(2SC1166-O or Y)			
R66	Carbon film 2.2k	RD1PS 222J	R70	Carbon film 68k	2SA726-F or G			
R67	Carbon film 12k	RD1PS 123J	R71	Positive coefficient thermistor	AEX-003			
R68	Carbon film 68k	RD1PS 683J	D1	Diode	1S2473			
R69	Carbon film 15k	RD1PS 153J	R72	Vacancy	(1S1555)			
R70	Carbon film 68k	RD1PS 683J	R73	Carbon film 2.2k	WZ-150			
R71	Carbon film 22	RD1PS 220J	R74	Carbon film 10k	WZ-130			
R72	Vacancy	R75	Carbon film 10k	1S2473			
R73	Carbon film 2.2k	RD1PS 222J	R76	Carbon film 10k	(1S1555)			
R74	Carbon film 10k	RD1PS 103J	R77	Carbon film 4.7k	1S2473			
R75	Carbon film 10k	RD1PS 103J	R78	Carbon film 4.7k	(1S1555)			
R76	Carbon film 10k	RD1PS 103J	R79	Carbon film 82k	1S2473			
R77	Carbon film 4.7k	RD1PS 472J	R80	Carbon film 82k	(1S1555)			
R78	Carbon film 4.7k	RD1PS 472J	D5	Diode	1S2473			
R79	Carbon film 82k	RD1PS 823J	D6	Diode	(1S1555)			
R80	Carbon film 82k	RD1PS 823J						



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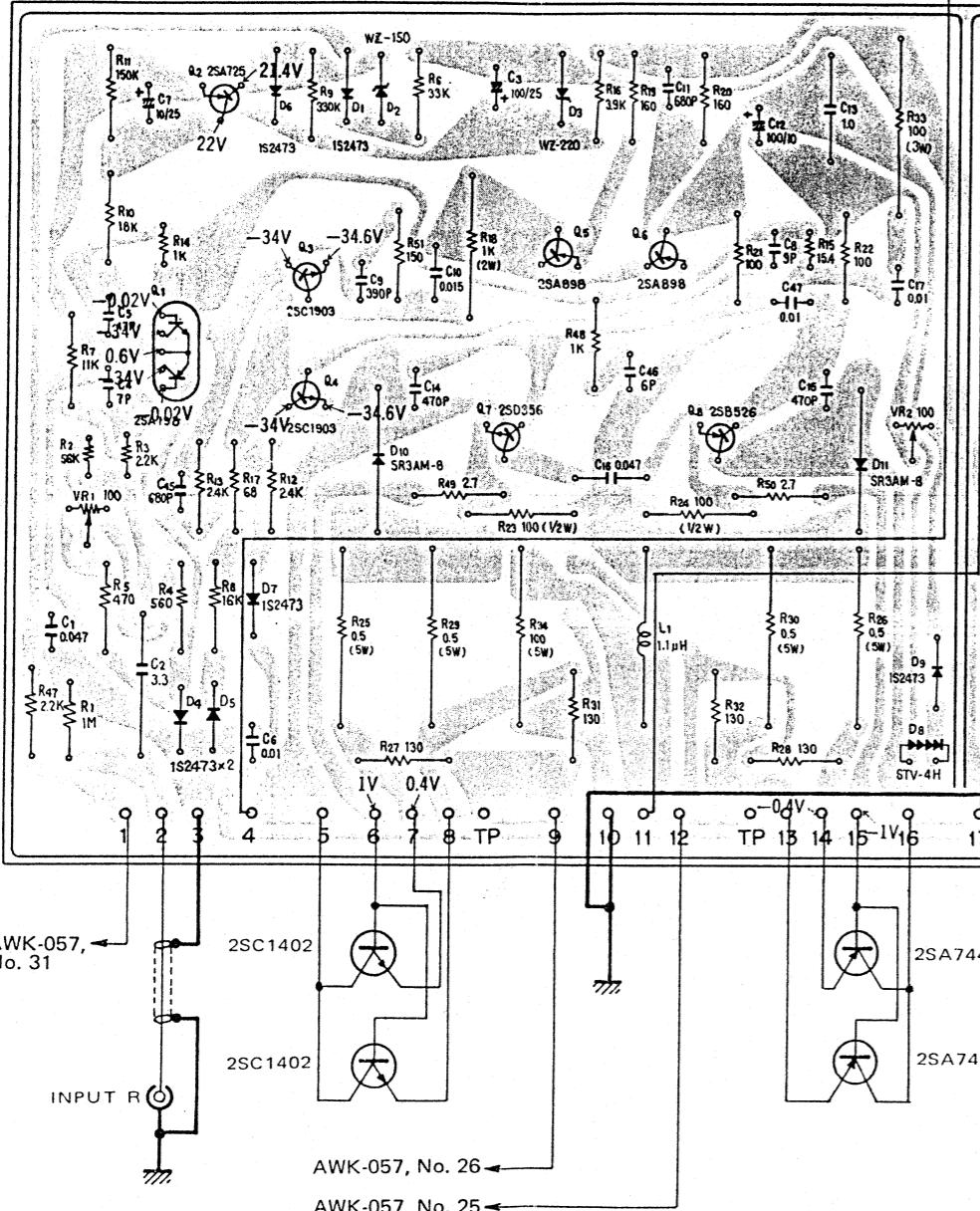
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9.5 AF POWER ASSEMBLY (AWK-058)

A



STEREO POWER AMPLIFIER

M-22

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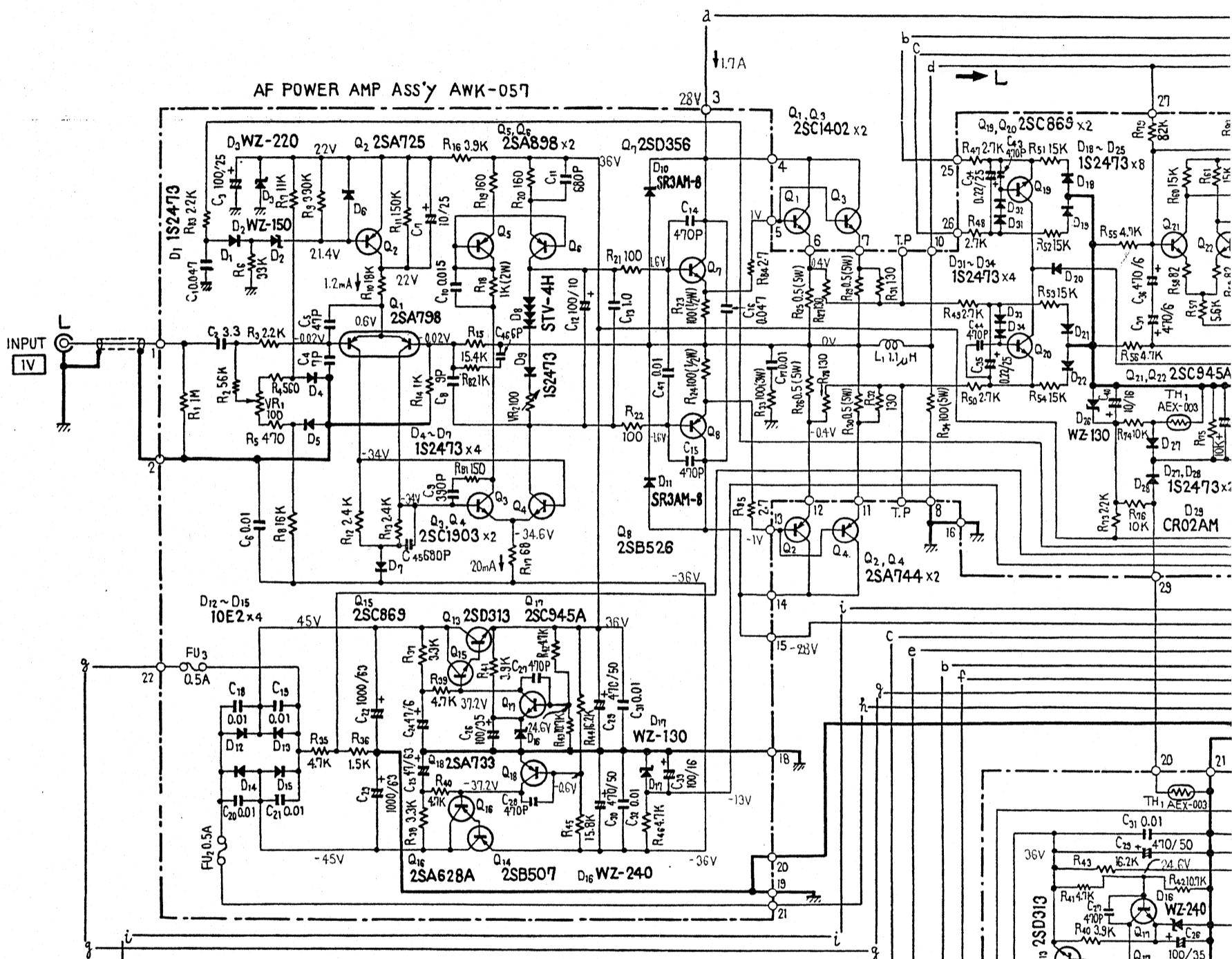
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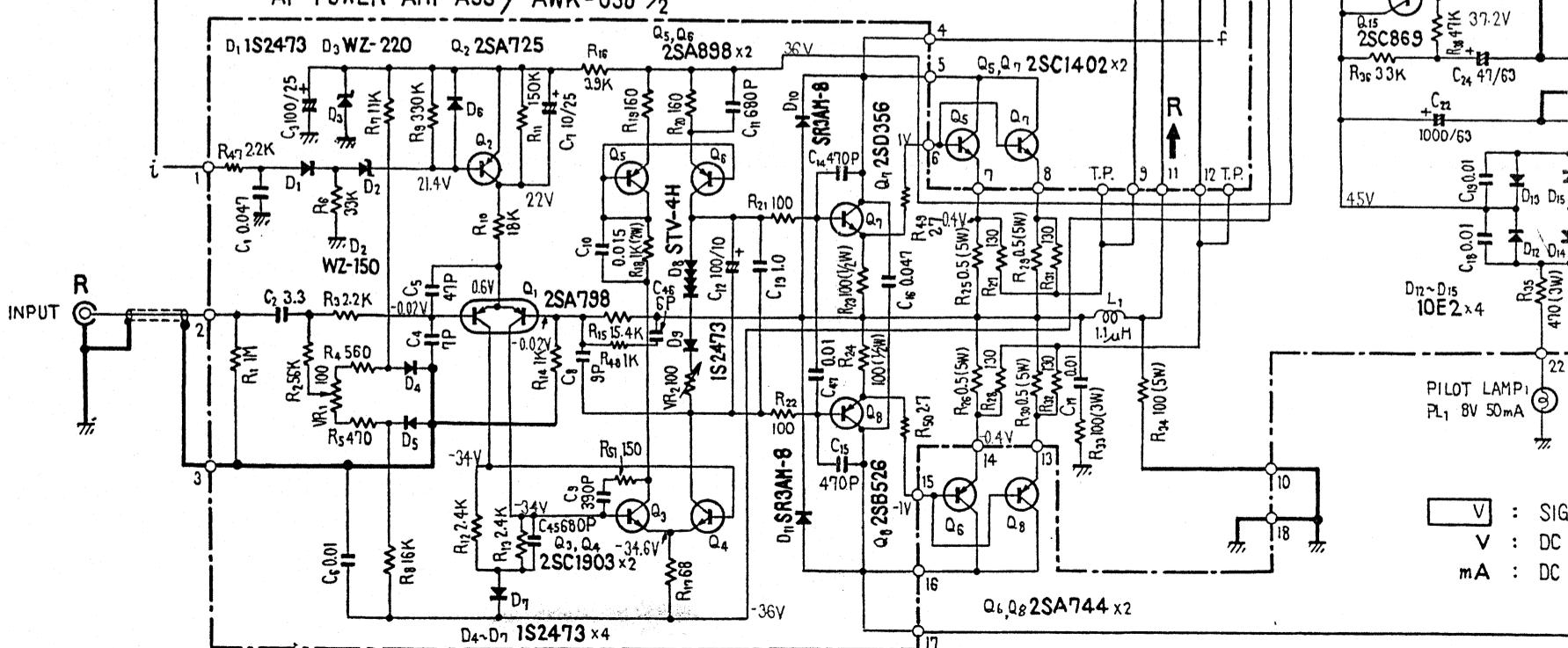
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AF POWER AMP ASS'Y AWK-057



AF POWER AMP ASS'Y AWK-058 1/2



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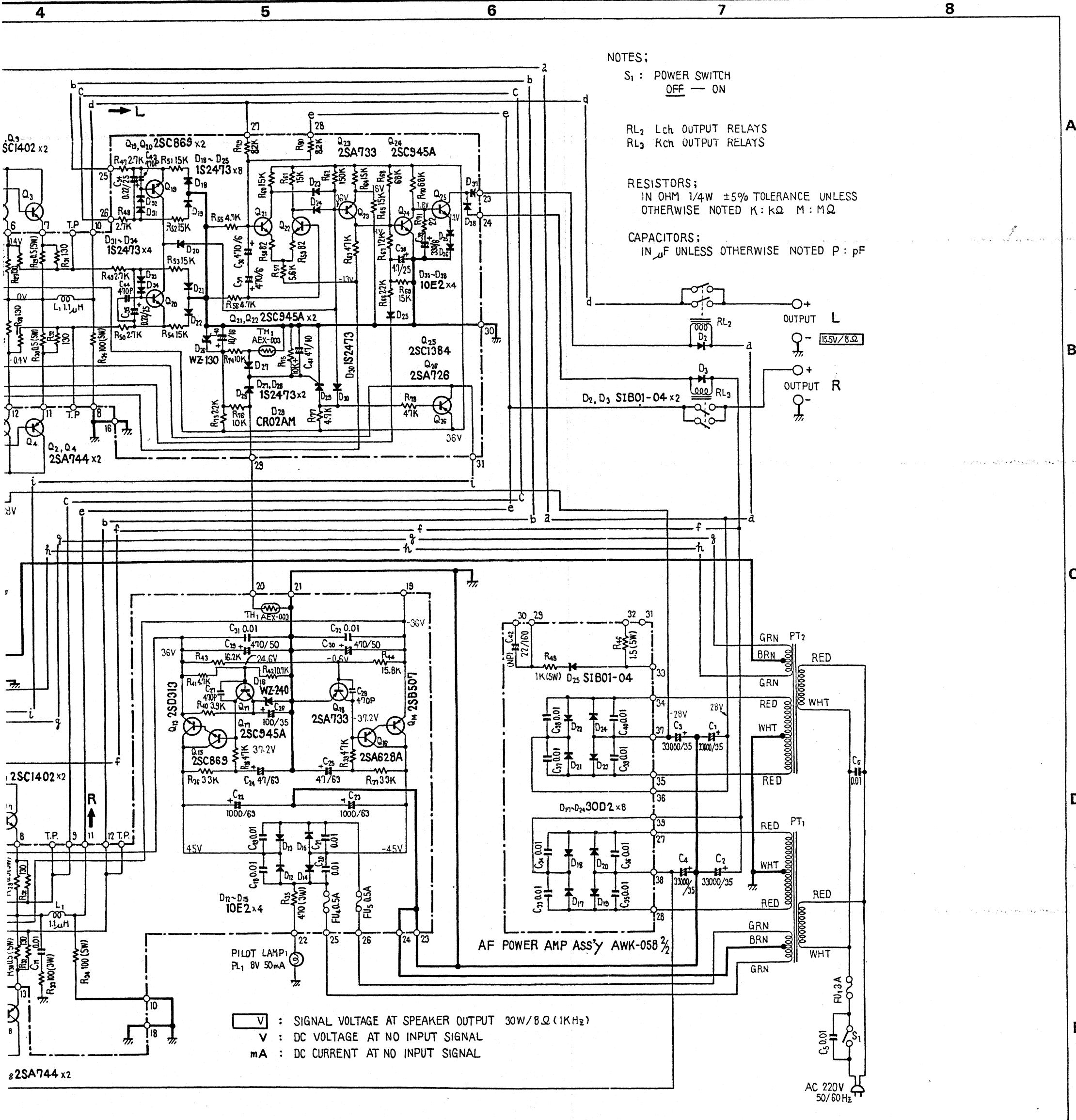
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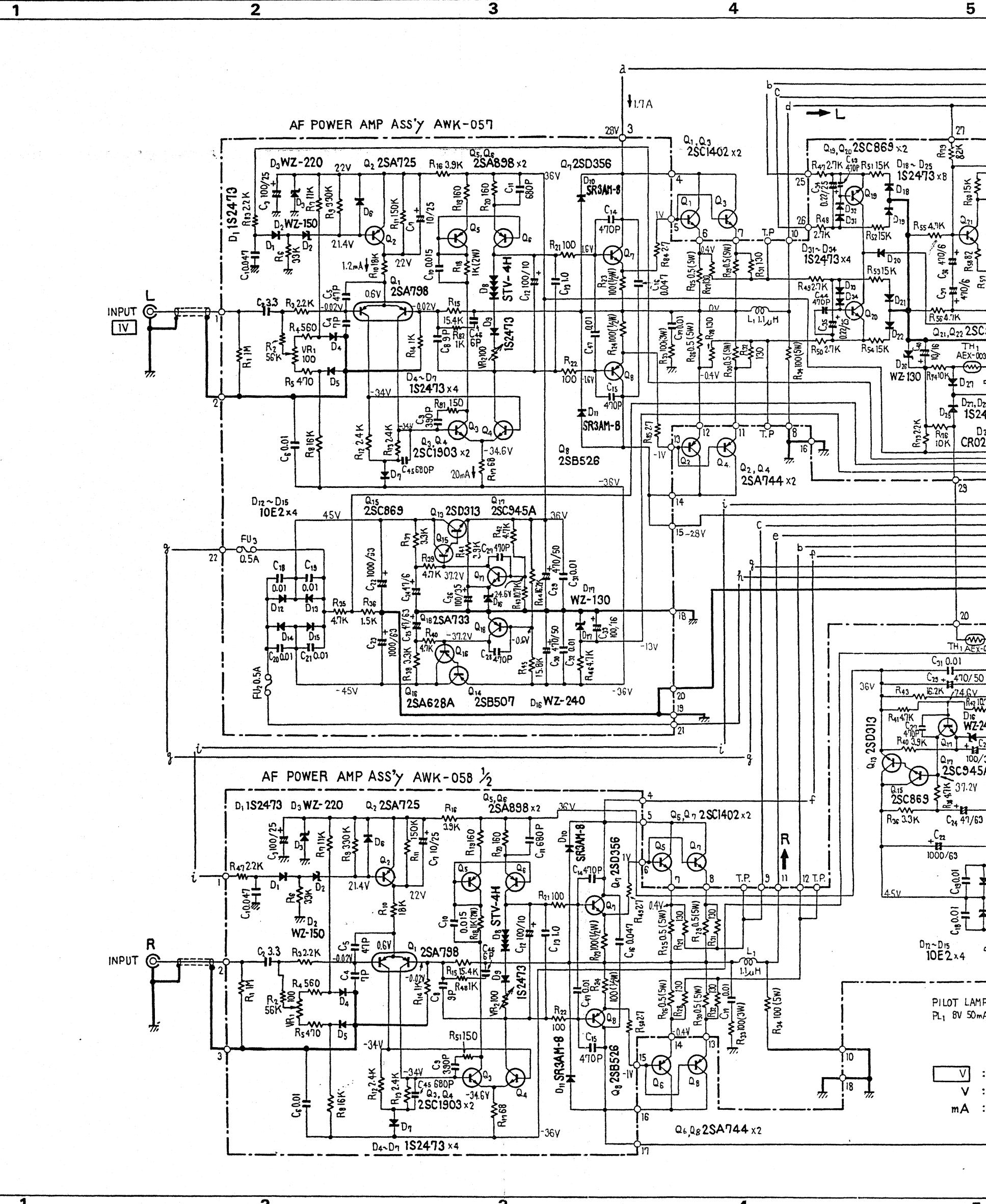
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mA : DC



STEREO POWER AMPLIFIER

M-22

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PIONEER

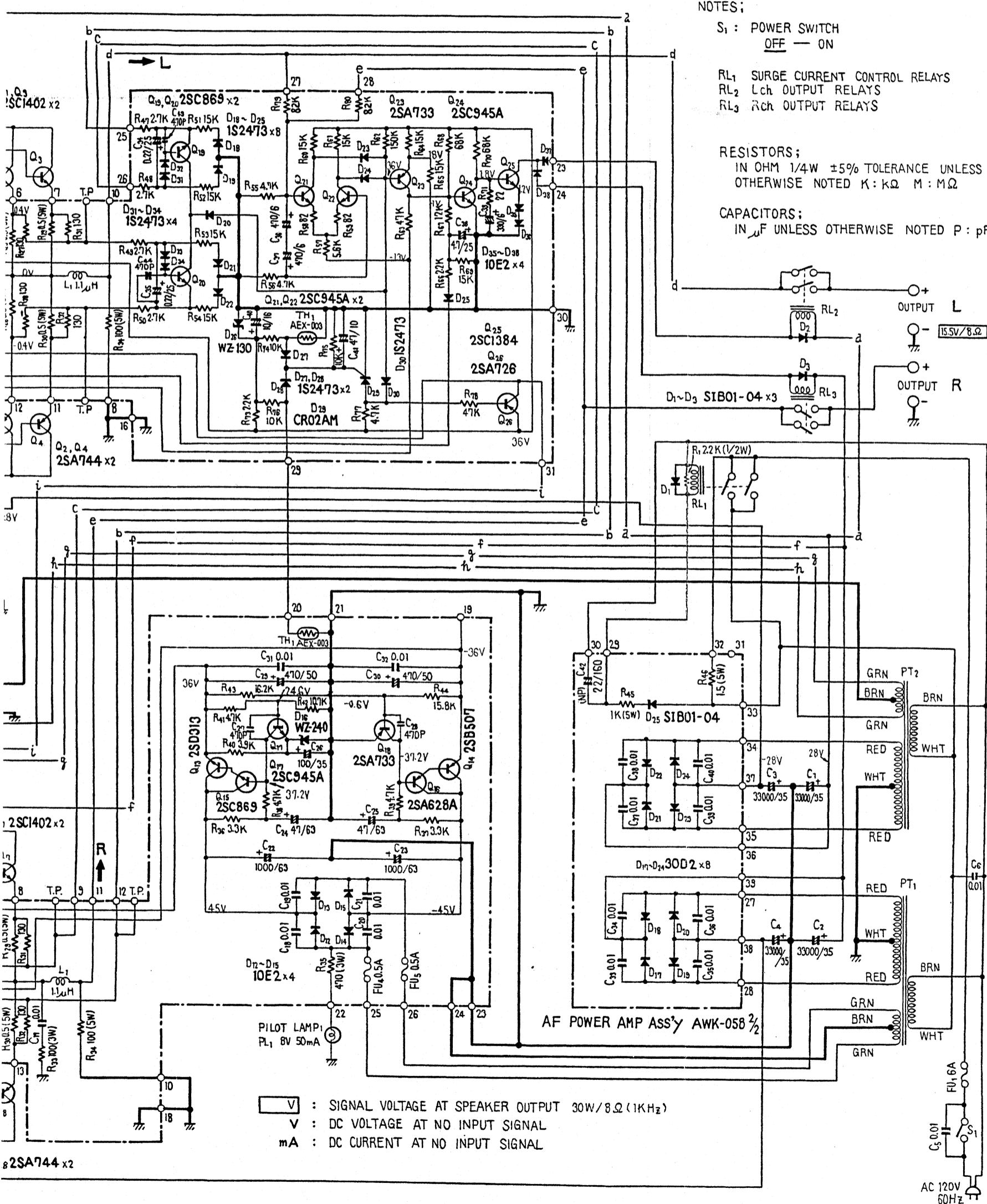
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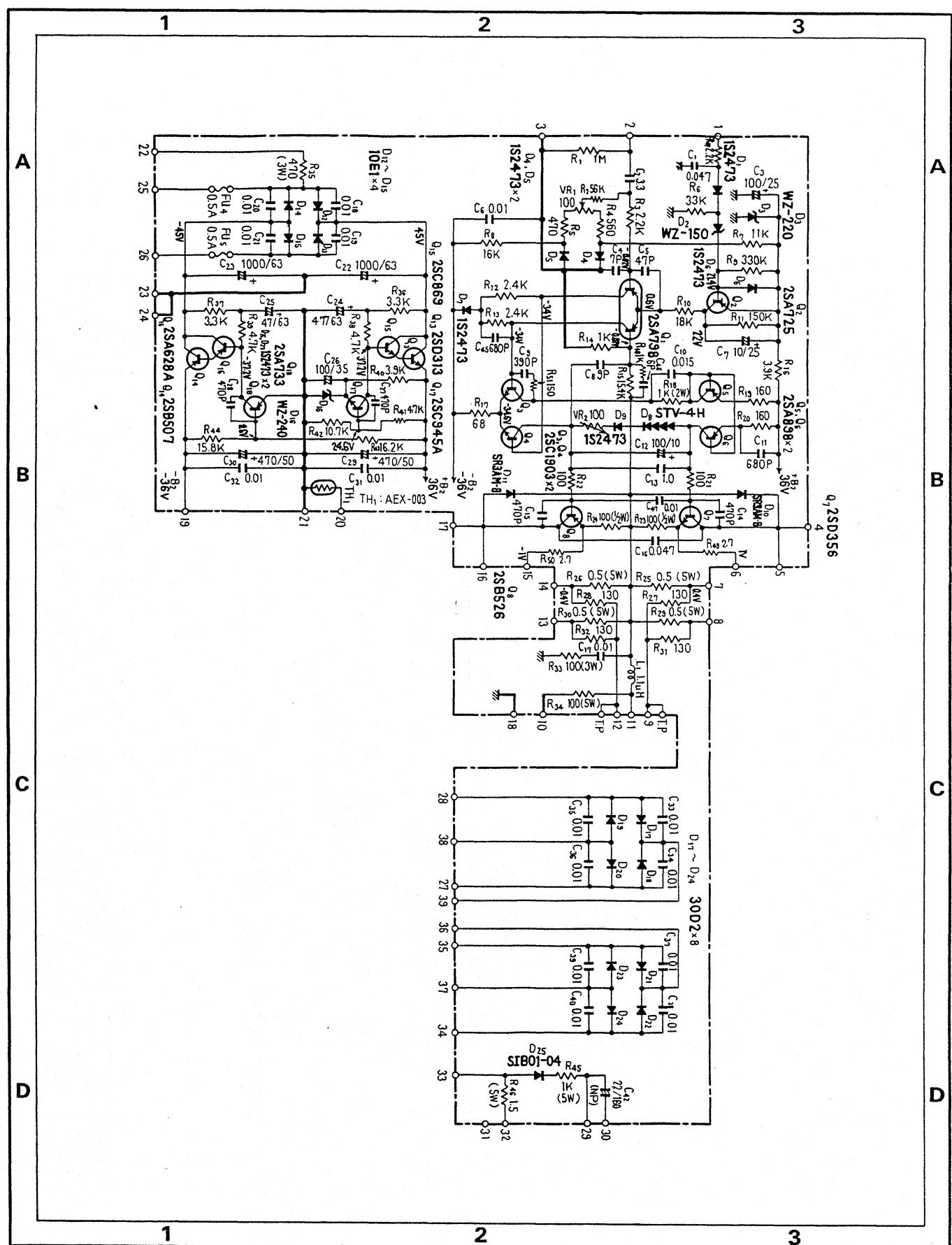
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Parts List of AF Power Assembly (AWK-058)

OTHERS

<u>Symbol</u>	<u>Description</u>	<u>Part No.</u>	<u>Symbol</u>	<u>Description</u>	<u>Part No.</u>
L1	AF choke coil 1.1μH	ATH-012	C41	Vacancy
	Fuse clip	AKR-013	C42	Electrolytic (NP) 22	160V ACH-322
	Contact strip 3P	AKM-033	C43	Vacancy
	Contact strip 4P	AKM-034	C44	Vacancy
	Contact strip 5P	AKM-035	C45	Ceramic	680p 50V CKDyb 681K 50
	Heat sink (small)	ANH-317	C46	Ceramic	6p 50V CCDSL 060F 50
	Sponge	AEC-387	C47	Mylar	0.01 50V CQMA 103J 50

CAPACITORS

<u>Symbol</u>	<u>Description</u>	<u>Part No.</u>	<u>Symbol</u>	<u>Description</u>	<u>Part No.</u>
C1	Mylar 0.047	50V CQMA 473J 50	RESISTORS		
C2	Metallized mylar 3.3	100V ACE-013	VR1	Semi-fixed 100-B	ACP-032
C3	Electrolytic 100	25V CEA 101P 25	VR2	Semi-fixed 100-B	ACP-032
C4	Ceramic 7p	50V CCDSL 070F 50	R1	Metal film 1M	RN½PT 1004G
C5	Ceramic 47p	50V CCDSL 470K 50	R2	Metal film 56k	RN1/5SQ 5602F
C6	Ceramic 0.01	50V CKDyf 103Z 50	R3	Metal film 2.2k	RN1/5SQ 2201F
C7	Electrolytic 10	25V CEA 100P 25	R4	Carbon film 560	RD½PS 561J
C8	Ceramic 9p	50V CCDSL 090F 50	R5	Carbon film 470	RD½PS 471J
C9	Ceramic 390p	50V CCDSL 391J 50	R6	Carbon film 33k	RD½PS 333J
C10	Mylar 0.015	50V CQMA 153J 50	R7	Carbon film 11k	RD½PS 113J
C11	Ceramic 680p	50V CKDyb 681K 50	R8	Carbon film 16k	RD½PS 163J
C12	Electrolytic 100	10V CEA 101P 10	R9	Carbon film 330k	RD½PS 334J
C13	Metallized mylar 1	100V ACE-008	R10	Carbon film 18k	RD½PS 183J
C14	Ceramic 470p	50V CKDyb 471K 50	R11	Carbon film 150k	RD½PS 154J
C15	Ceramic 470p	50V CKDyb 471K 50	R12	Carbon film 2.4k	RD½PS 242J
C16	Mylar 0.047	100V CQMA 473J 100	R13	Carbon film 2.4k	RD½PS 242J
C17	Mylar 0.01	50V CQMA 103J 50	R14	Metal film 1k	1/5W RN1/5SQ 1001F
C18	Ceramic 0.01	150V ACG-004	R15	Metal film 15.4k	1/5W RN1/5SQ 1542F
C19	Ceramic 0.01	150V ACG-004	R16	Carbon film 3.9k	RD½PS 392J
C20	Ceramic 0.01	150V ACG-004	R17	Carbon film 68	RD½PS 680J
C21	Ceramic 0.01	150V ACG-004	R18	Metal oxide 1k	2W RS2P 102J
C22	Electrolytic 1000	63V ACH-319	R19	Carbon film 160	RD½PS 161J
C23	Electrolytic 1000	63V ACH-319	R20	Carbon film 160	RD½PS 161J
C24	Electrolytic 47	63V CEA 470P 63	R21	Carbon film 100	RD½PS 101J
C25	Electrolytic 47	63V CEA 470P 63	R22	Carbon film 100	RD½PS 101J
C26	Electrolytic 100	35V CEA 101P 35	R23	Carbon film 100	½W RD½PSF 101J
C27	Ceramic 470p	50V CKDyb 471K 50	R24	Carbon film 100	½W RD½PSF 101J
C28	Ceramic 470p	50V CKDyb 471K 50	R25	Wire wound 0.5	5W RT5B 0R5K
C29	Electrolytic 470	50V CEB 471P 50	R26	Wire wound 0.5	5W RT5B 0R5K
C30	Electrolytic 470	50V CEB 471P 50	R27	Carbon film 130	RD½PS 131J
C31	Ceramic 0.01	50V CKDyf 103Z 50	R28	Carbon film 130	RD½PS 131J
C32	Ceramic 0.01	50V CKDyf 103Z 50	R29	Wire wound 0.5	5W RT5B 0R5K
C33	Ceramic 0.01	150V ACG-004	R30	Wire wound 0.5	5W RT5B 0R5K
C34	Ceramic 0.01	150V ACG-004	R31	Carbon film 130	RD½PS 131J
C35	Ceramic 0.01	150V ACG-004	R32	Carbon film 130	RD½PS 131J
C36	Ceramic 0.01	150V ACG-004	R33	Metal oxide 100	3W RS3P 101J
C37	Ceramic 0.01	150V ACG-004	R34	Wire wound 100	5W RT5B 101K
C38	Ceramic 0.01	150V ACG-004	R35	Metal oxide 470	3W RS3P 471J

<u>Symbol</u>	<u>Description</u>		<u>Part No.</u>	<u>Symbol</u>	<u>Description</u>		<u>Part No.</u>
R36	Carbon film	33k	RD%PS 333J	D7	Diode		1S2473
R37	Carbon film	33k	RD%PS 333J				(1S1555)
R38	Carbon film	47k	RD%PS 473J	D8	Varistor		STV-4H
R39	Carbon film	47k	RD%PS 473J	D9	Diode		1S2473
R40	Carbon film	3.9k	RD%PS 392J				(1S1555)
R41	Metal film	4.7k	1/5W	RN1/5SQ 4701F	D10	Diode	SR3AM-8
R42	Metal film	10.7k	1/5W	RN1/5SQ 1072F	D11	Diode	SR3AM-8
R43	Metal film	16.2k	1/5W	RN1/5SQ 1622F	D12	Diode	10E2
R44	Metal film	15.8k	1/5W	RN1/5SQ 1582F			(1S1885)
R45	Wire wound	1k	5W	RT5B 102K	D13	Diode	10E2
							(1S1885)
R46	Wire wound	1.5	5W	RT5B 1R5K	D14	Diode	10E2
R47	Carbon film	2.2k		RD%PS 222J			(1S1885)
R48	Carbon film	1k		RD%PS 102J	D15	Diode	10E2
R49	Carbon film	2.7		RD%PS 2R7J			(1S1885)
R50	Carbon film	2.7		RD%PS 2R7J	D16	Zener diode	WZ-240
R51	Carbon film	150		RD%PS 151J	D17	Diode	30D2
					D18	Diode	(SR3AM-4)
							30D2
							(SR3AM-4)
SEMICONDUCTORS							
<u>Symbol</u>	<u>Description</u>		<u>Part No.</u>	<u>Symbol</u>	<u>Description</u>		<u>Part No.</u>
Q1	Transistor		2SA798-F or G	D19	Diode		30D2
Q2	Transistor		2SA725-F or G	D20	Diode		(SR3AM-4)
Q3	Transistor		2SC1903-B or V				30D2
Q4	Transistor		2SC1903-B or V				(SR3AM-4)
Q5	Transistor		2SA898-B or V	D21	Diode		30D2
							(SR3AM-4)
Q6	Transistor		2SA898-B or V	D22	Diode		30D2
Q7*	Transistor		2SD356-D or C				(SR3AM-4)
Q8*	Transistor		2SB526-D or C				30D2
				D23	Diode		(SR3AM-4)
*	* hfe of Q7 and Q8 should have the same value (matched pair).						
Q13	Transistor		2SD313-D or E	D24	Diode		30D2
Q14	Transistor		2SB507-D or E				(SR3AM-4)
Q15	Transistor		2SC869-D or C	D25	Diode		SIB01-04
Q16	Transistor		2SA628A-D or C				
Q17	Transistor		2SC945A-P or Q (2SC1647-P or Q)				
Q18	Transistor		2SA733-R or Q (2SA823-P or Q)				
TH1	Positive coefficient thermistor		AEX-003				
D1	Diode		1S2473 (1S1555)				
D2	Zener diode		WZ-150				
D3	Zener diode		WZ-220				
D4	Diode		1S2473 (1S1555)				
D5	Diode		1S2473 (1S1555)				
D6	Diode		1S2473 (1S1555)				

10. PACKING

